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|  | Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFL111LW | | Page 1 (96) |
| | Author Data Daoud Attayi | Dates of Test Feb. 17, June 28, Dec. 17-18, 2012 | Report No RTS-6026-1302-03 |

Annex A: Measurement data and plots

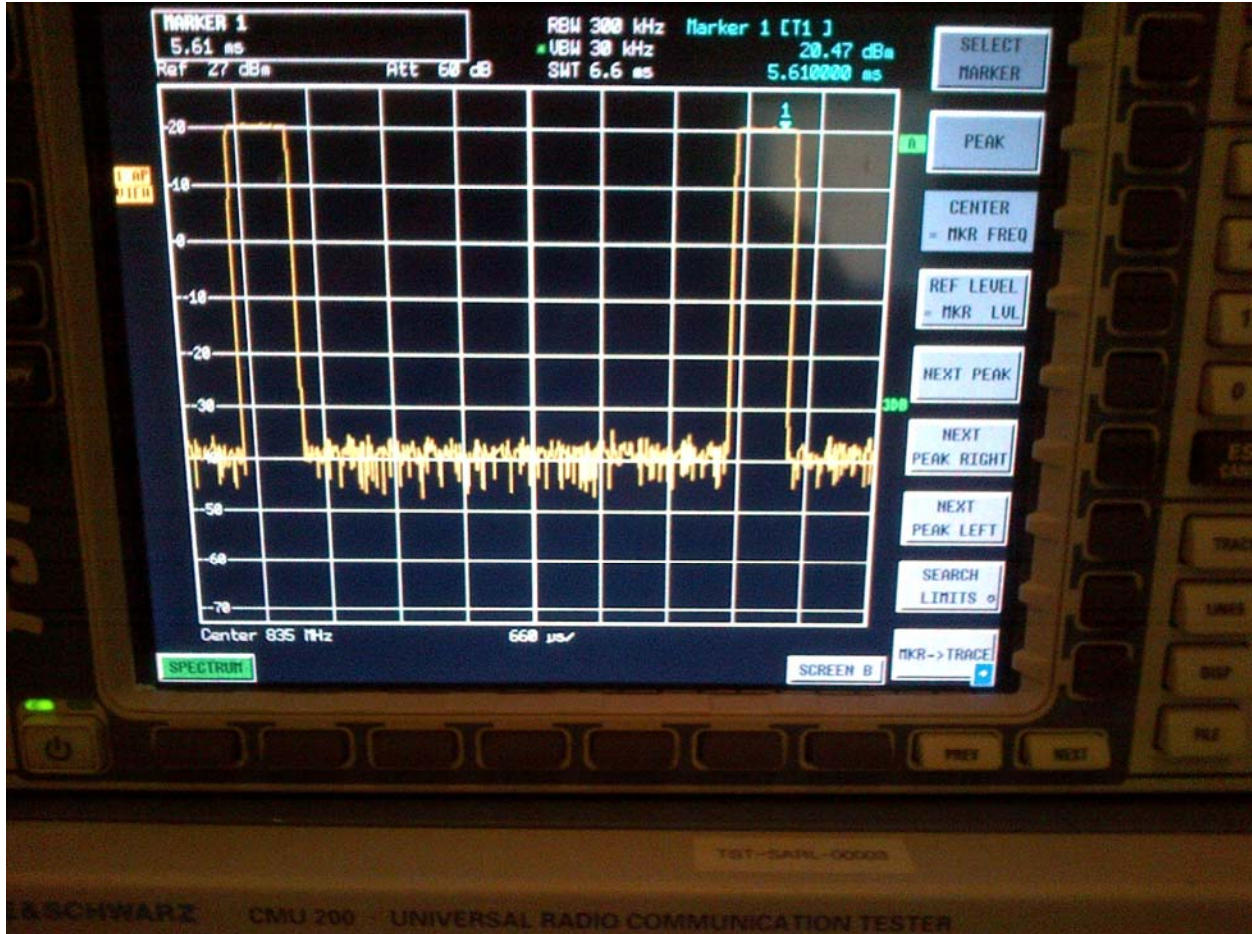
A.1 Spectrum analyser plots: GSM/UMTS, CW, 80%AM, signals

Author Data
Daoud Attayi

Dates of Test
Feb. 17, June 28, Dec. 17-18, 2012

Report No
RTS-6026-1302-03

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L6ARFL110LW



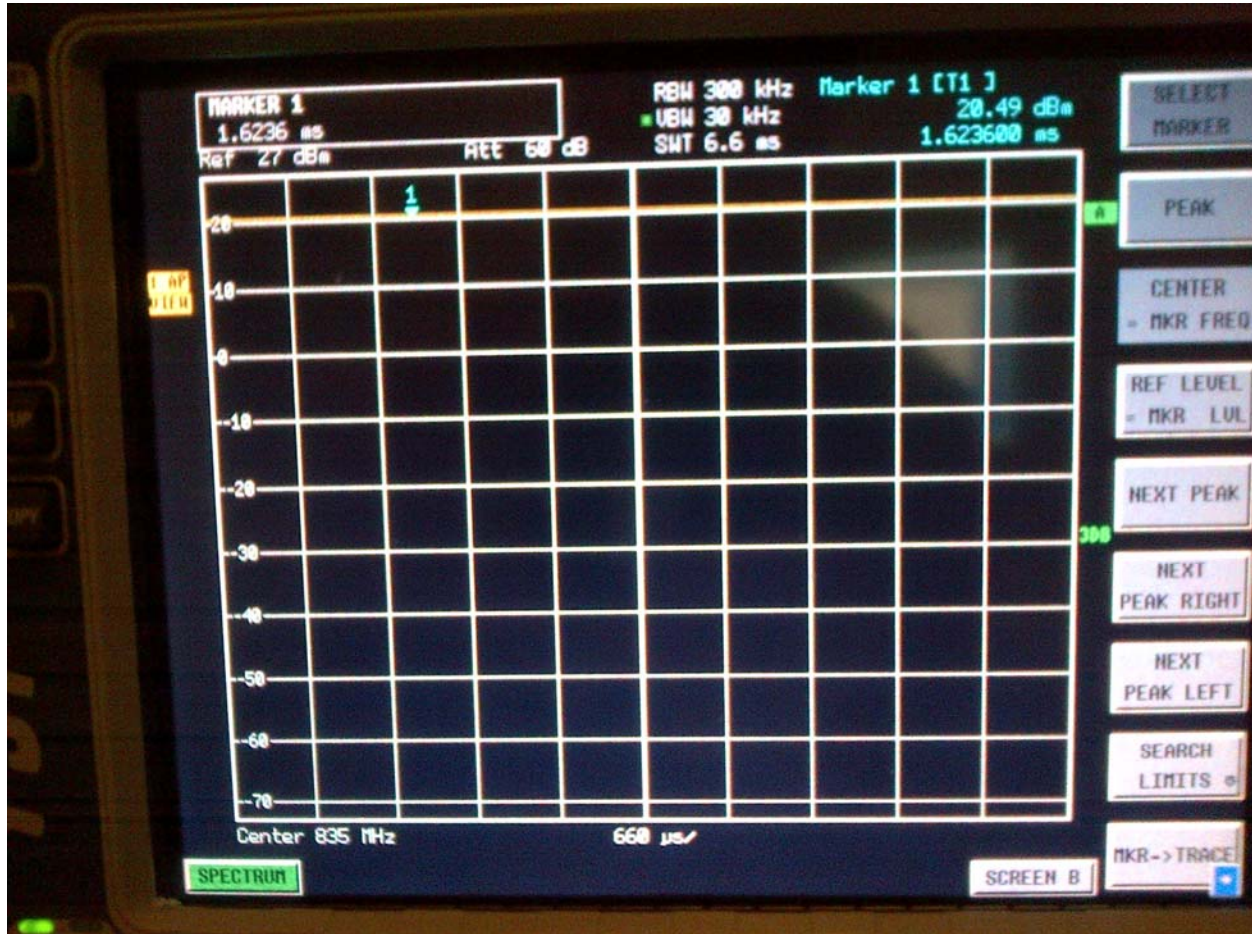
GSM 835 MHz

Author Data
Daoud Attayi

Dates of Test
Feb. 17, June 28, Dec. 17-18, 2012

Report No
RTS-6026-1302-03

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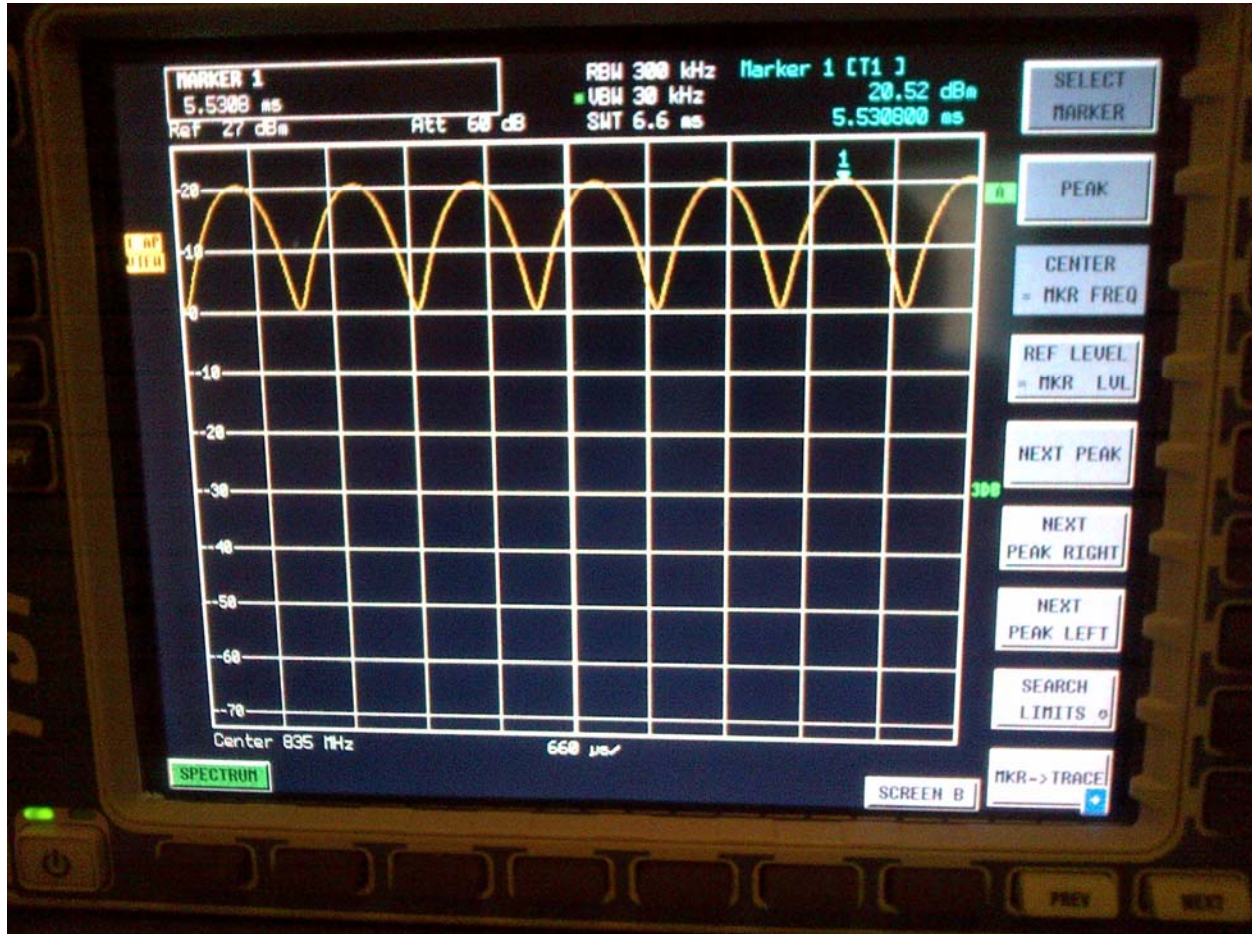
CW 835 MHz

Author Data
Daoud Attayi

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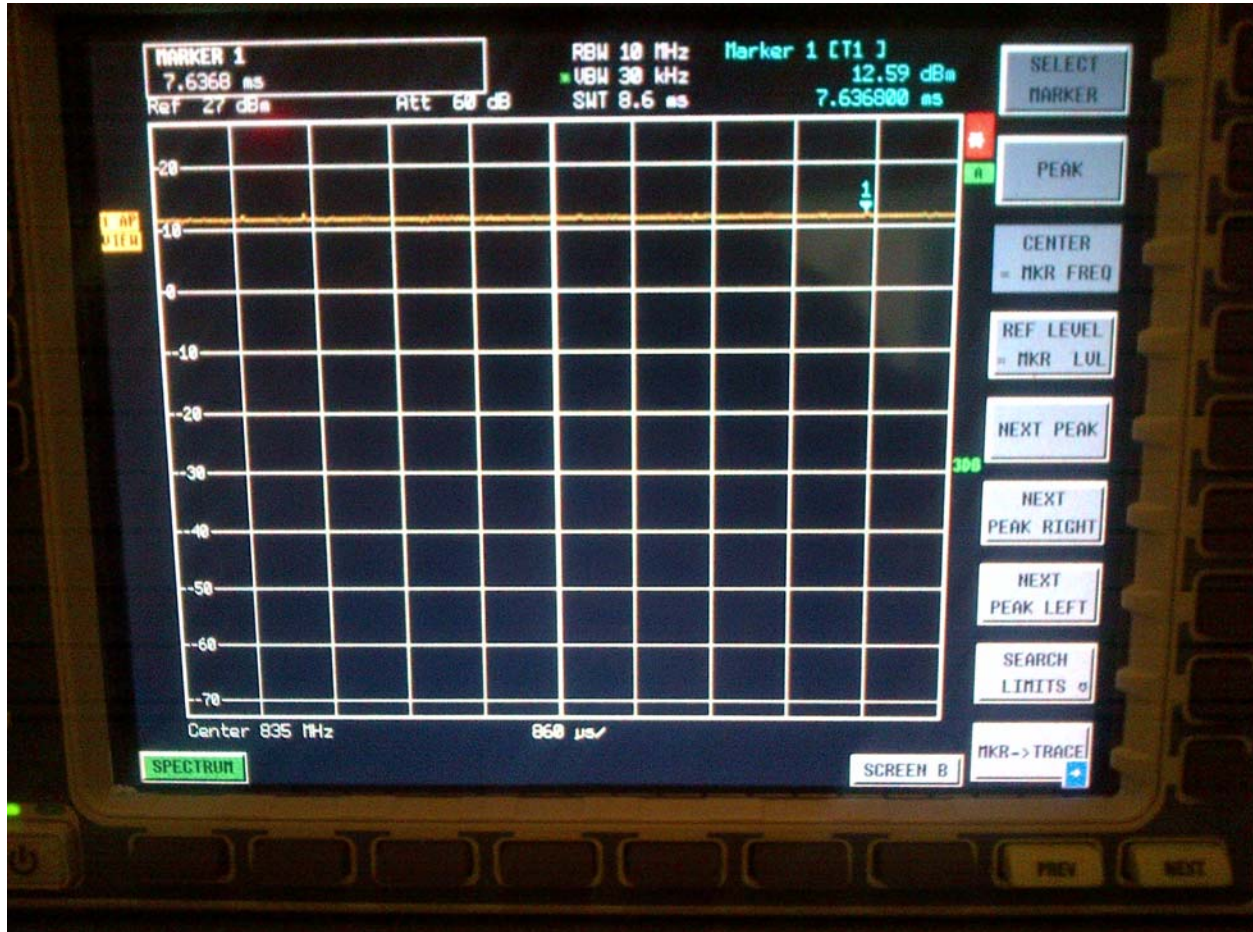
AM 80% 835 MHz

Author Data
Daoud Attayi

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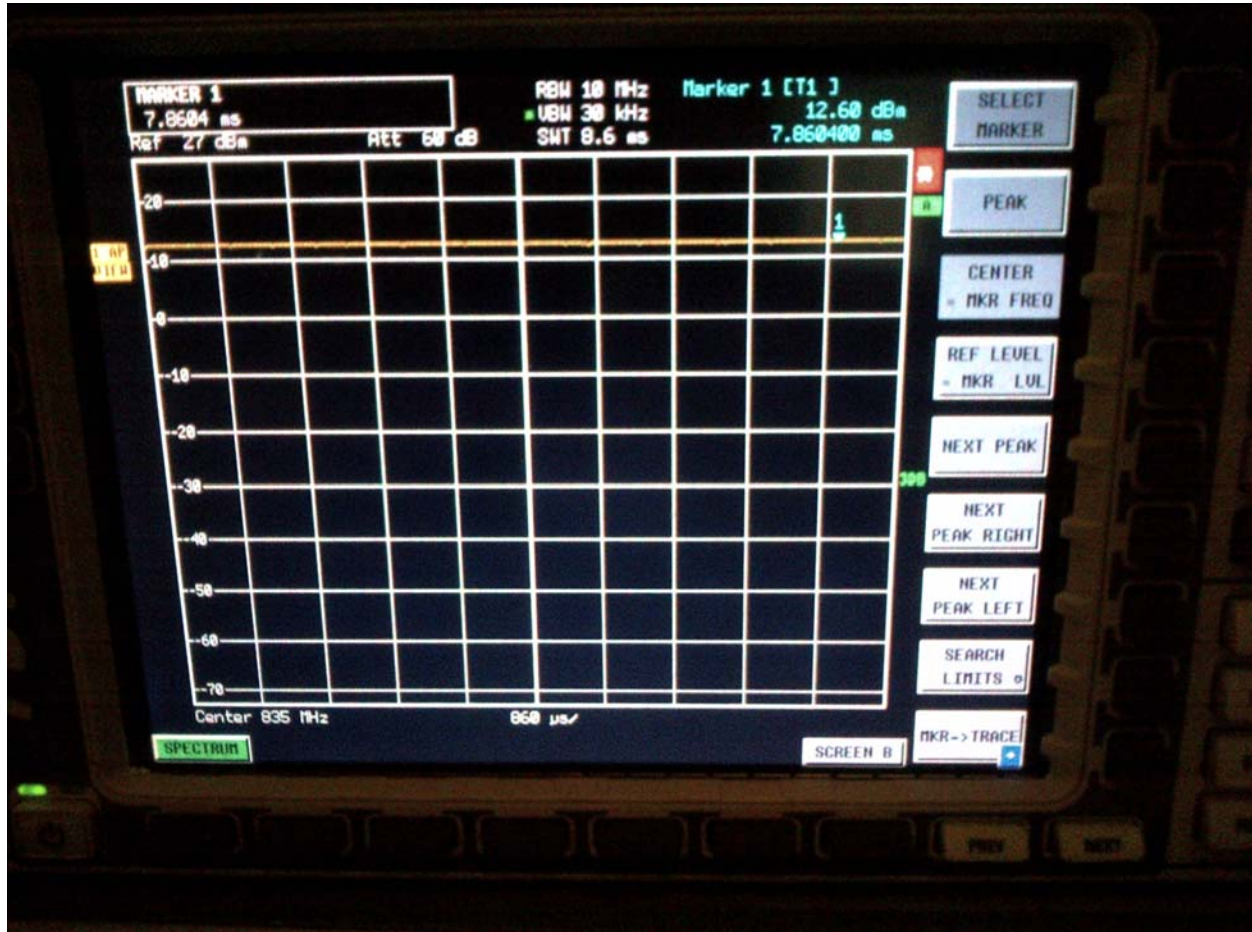
UMTS 835 MHz

Author Data
Daoud Attayi

Dates of Test
Feb. 17, June 28, Dec. 17-18, 2012

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RTS-6026-1302-03

FCC ID
L6ARFL110LW



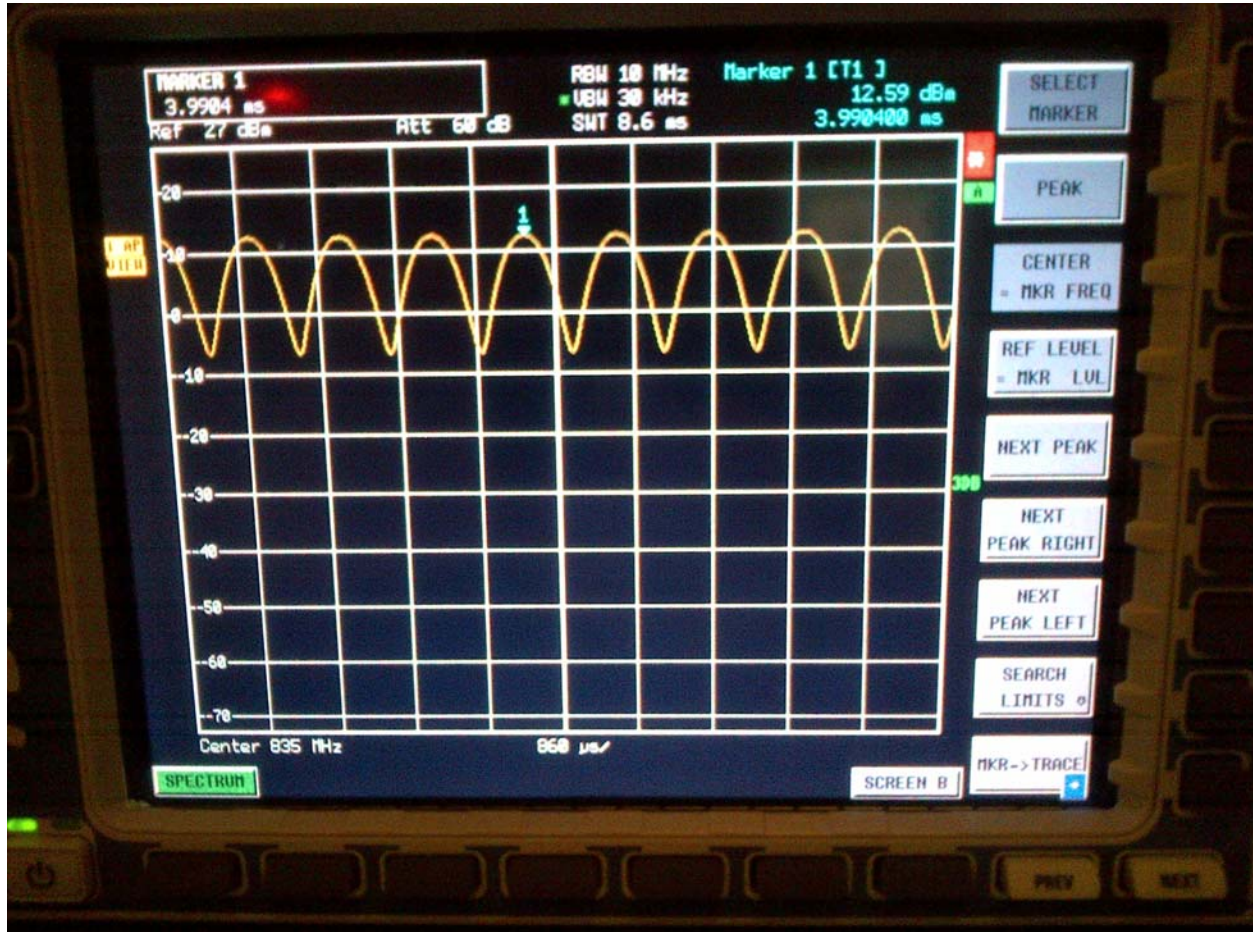
CW 835 MHz

Author Data
Daoud Attayi

Dates of Test
Feb. 17, June 28, Dec. 17-18, 2012

Report No
RTS-6026-1302-03

FCC ID
L6ARFL110LW



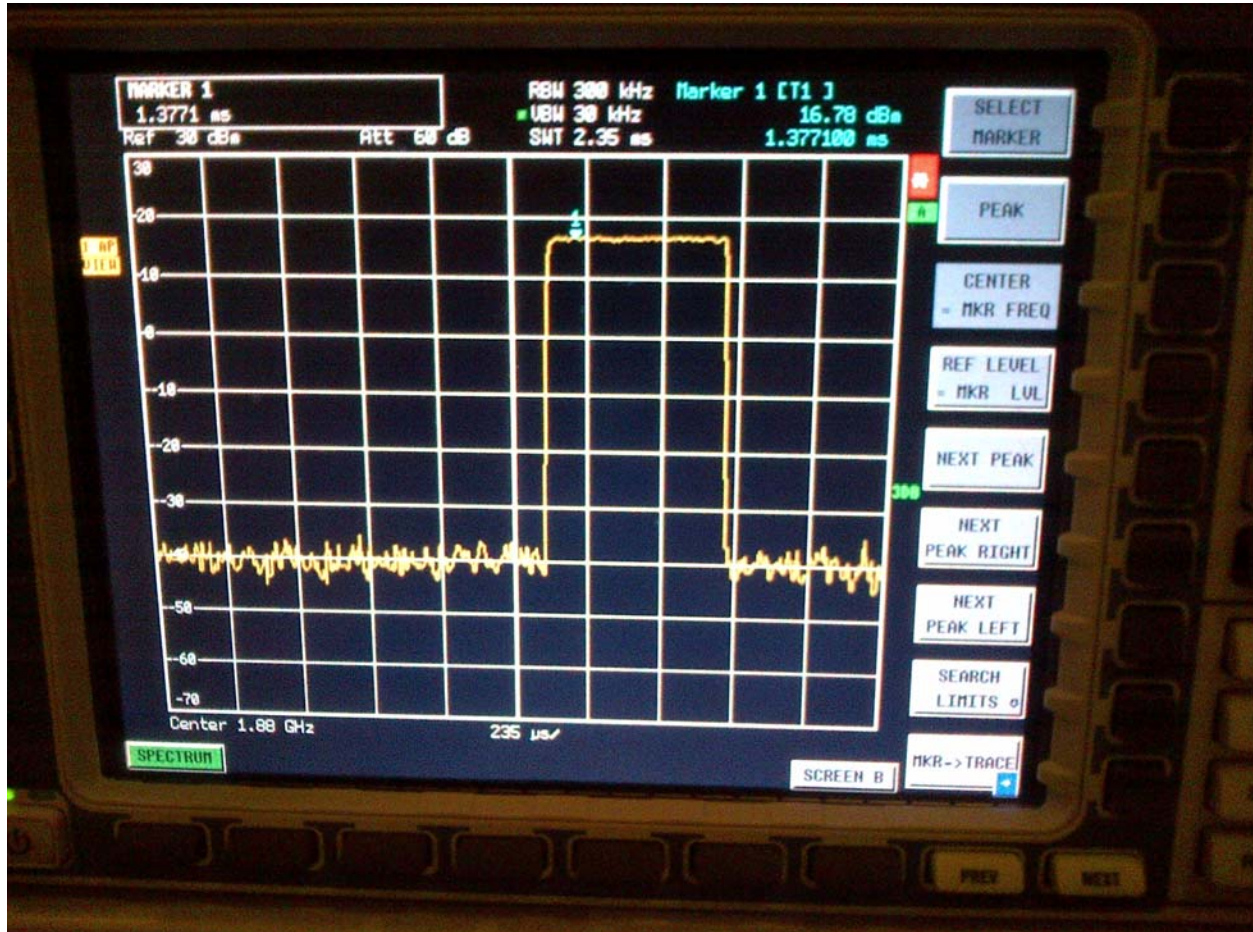
AM 80% 835 MHz

Author Data
Daoud Attayi

Dates of Test
Feb. 17, June 28, Dec. 17-18, 2012

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RTS-6026-1302-03

FCC ID
L6ARFL110LW



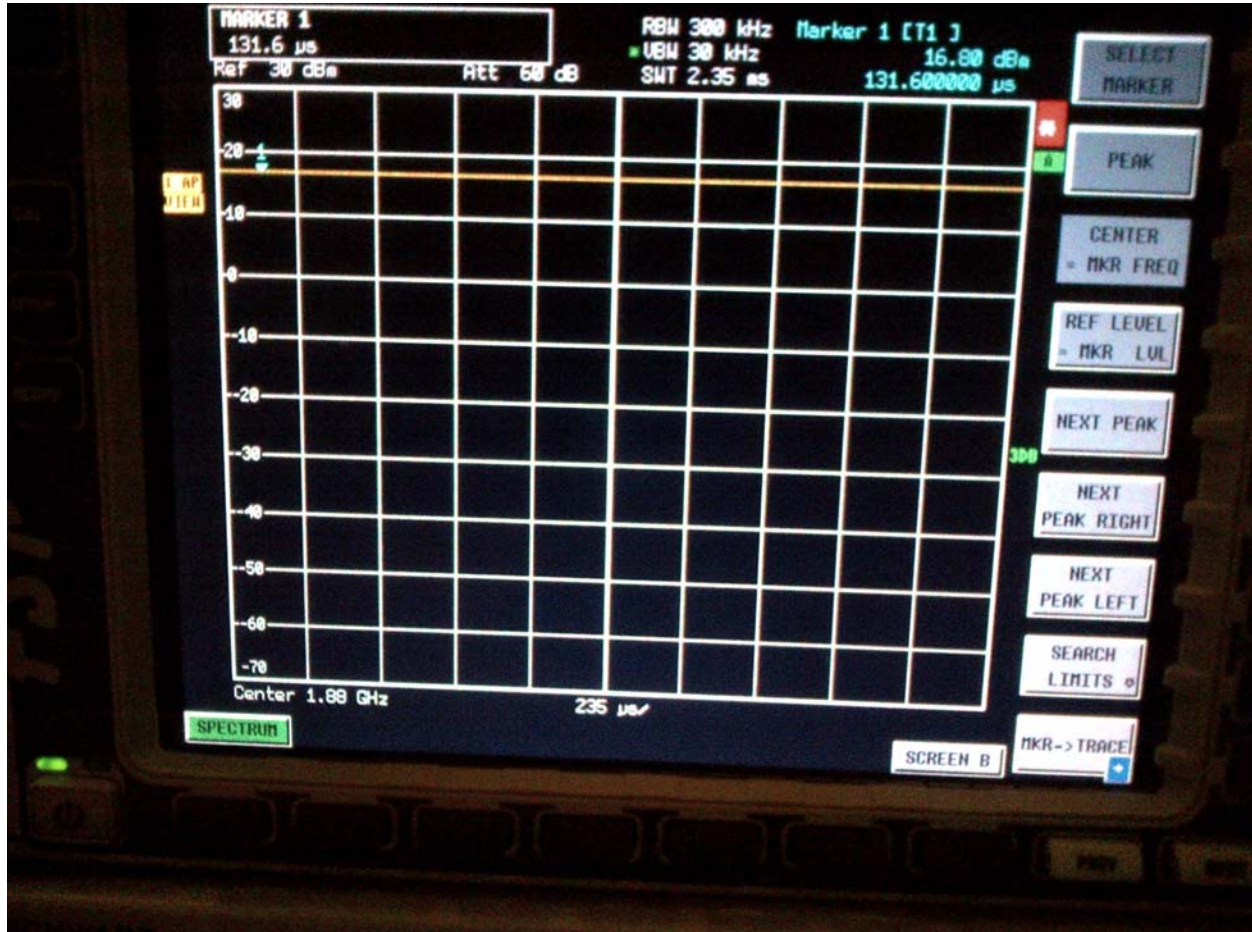
GSM 1880 MHz

Author Data
Daoud Attayi

Dates of Test
Feb. 17, June 28, Dec. 17-18, 2012

Report No
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CW 1880 MHz

Author Data
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Dates of Test
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AM 80 % 1880 MHz

Author Data
Daoud Attayi

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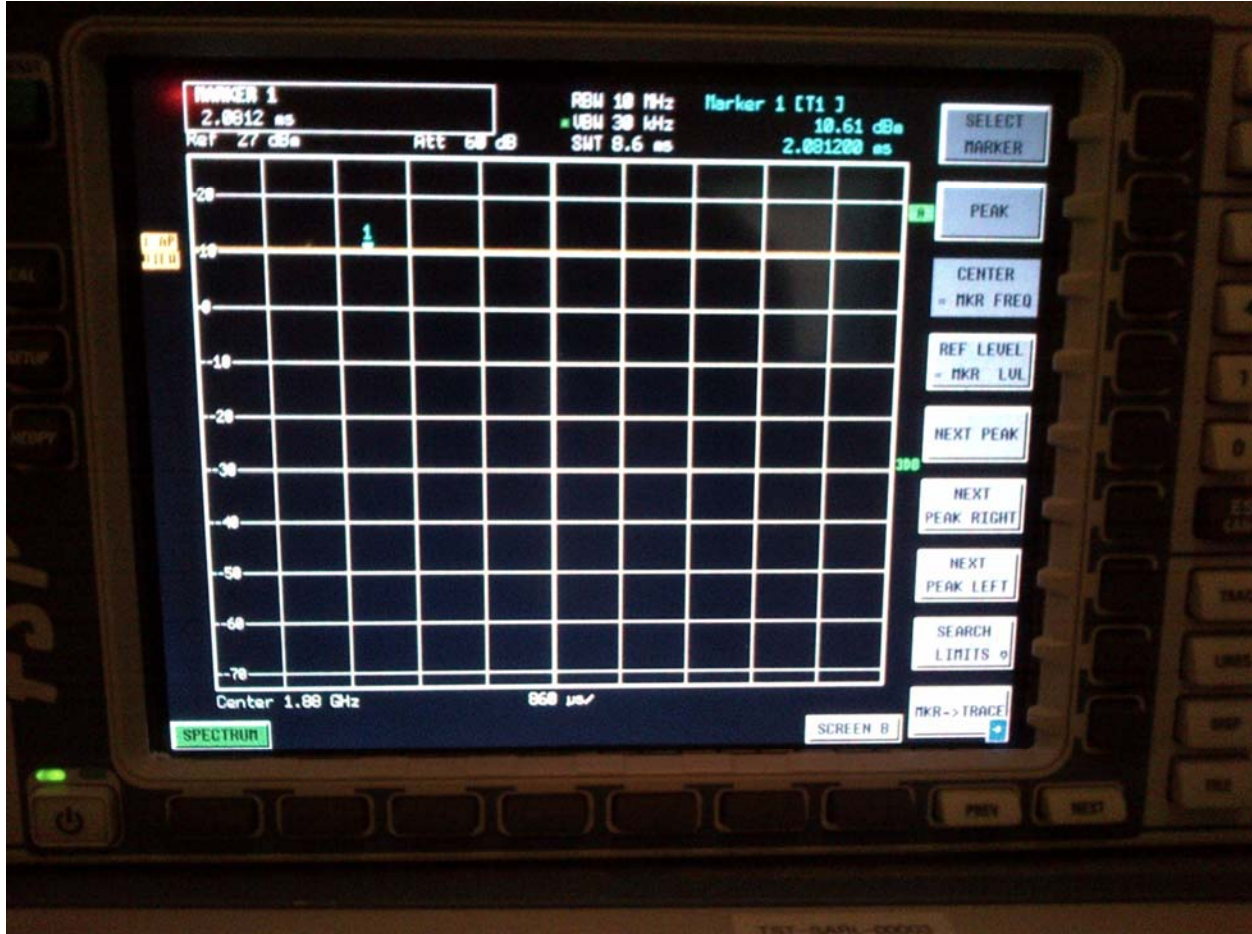
UMTS 1880 MHz

Author Data
Daoud Attayi

Dates of Test
Feb. 17, June 28, Dec. 17-18, 2012

Report No
RTS-6026-1302-03

FCC ID
L6ARFL110LW



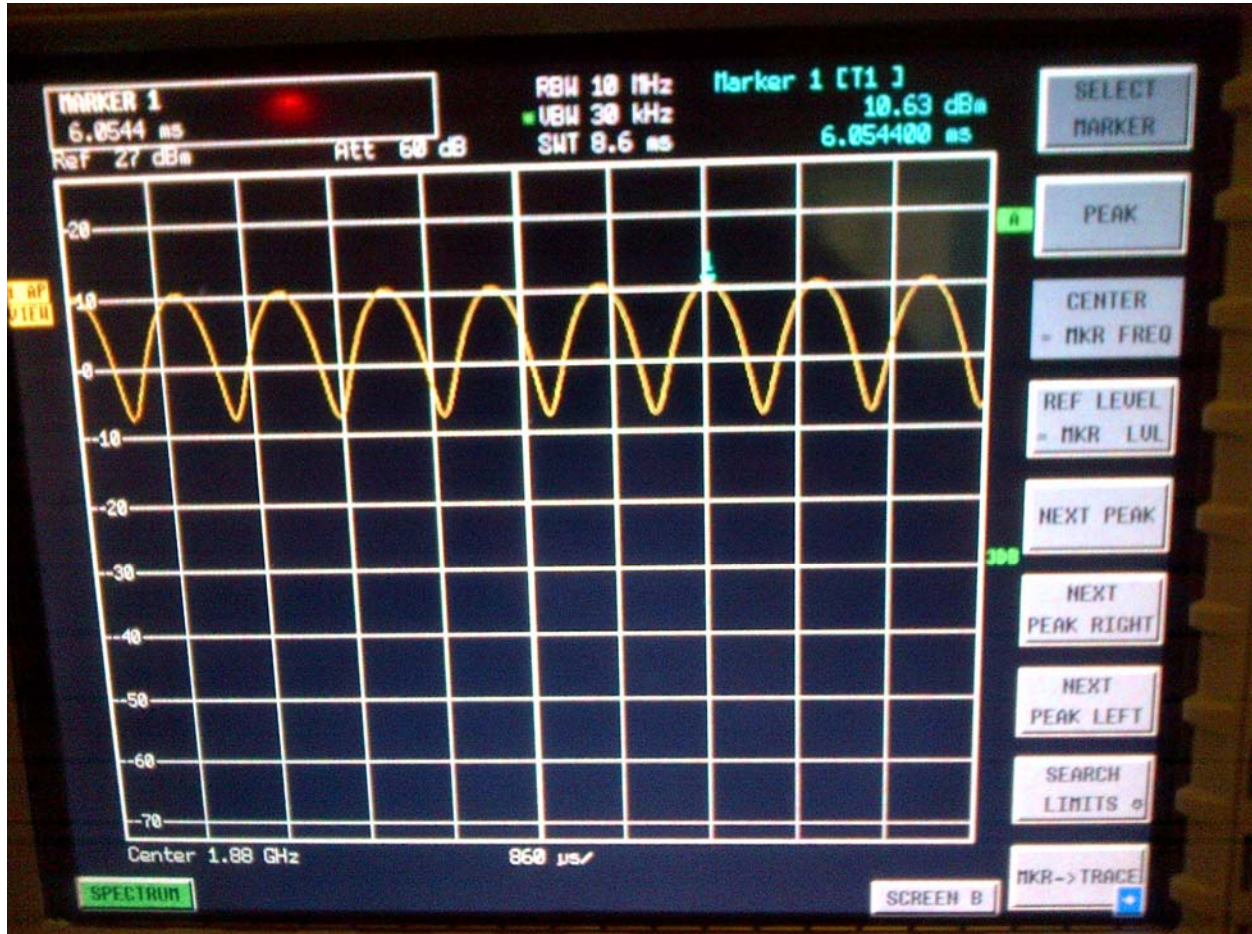
CW 1880 MHz

Author Data
Daoud Attayi


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AM 80 % 1880 MHz

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A.2 Dipole validation and probe modulation factor plots

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|  | Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFL111LW | | Page 15 (96) |
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Date/Time: 12/17/2012 11:31:29 PM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_validation_835 MHz_12_17_12

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: 1011

Communication System: CW; Frequency: 835 MHz
 Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³
 Phantom section: RF Section
 Measurement Standard: DASYS (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/9/2012
- Sensor-Surface: (Fix Surface), z = 4.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASYS2 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole E-Field measurement/E Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test

(41x361x1): Measurement grid: dx=5mm, dy=5mm
 Device Reference Point: 0, 0, -6.3 mm
 Reference Value = 106.6 V/m; Power Drift = -0.02 dB
 PMR not calibrated. PMF = 1.000 is applied.
 E-field emissions = 168.4 V/m
Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

| | | |
|--------------------------------------|--------------------------------------|--------------------------------------|
| Grid 1 M4 144.2 V/m | Grid 2 M4 154.3 V/m | Grid 3 M4 154.2 V/m |
| Grid 4 M4 80.47 V/m | Grid 5 M4 83.31 V/m | Grid 6 M4 81.66 V/m |
| Grid 7 M4 | Grid 8 M4 | Grid 9 M4 |

Author Data
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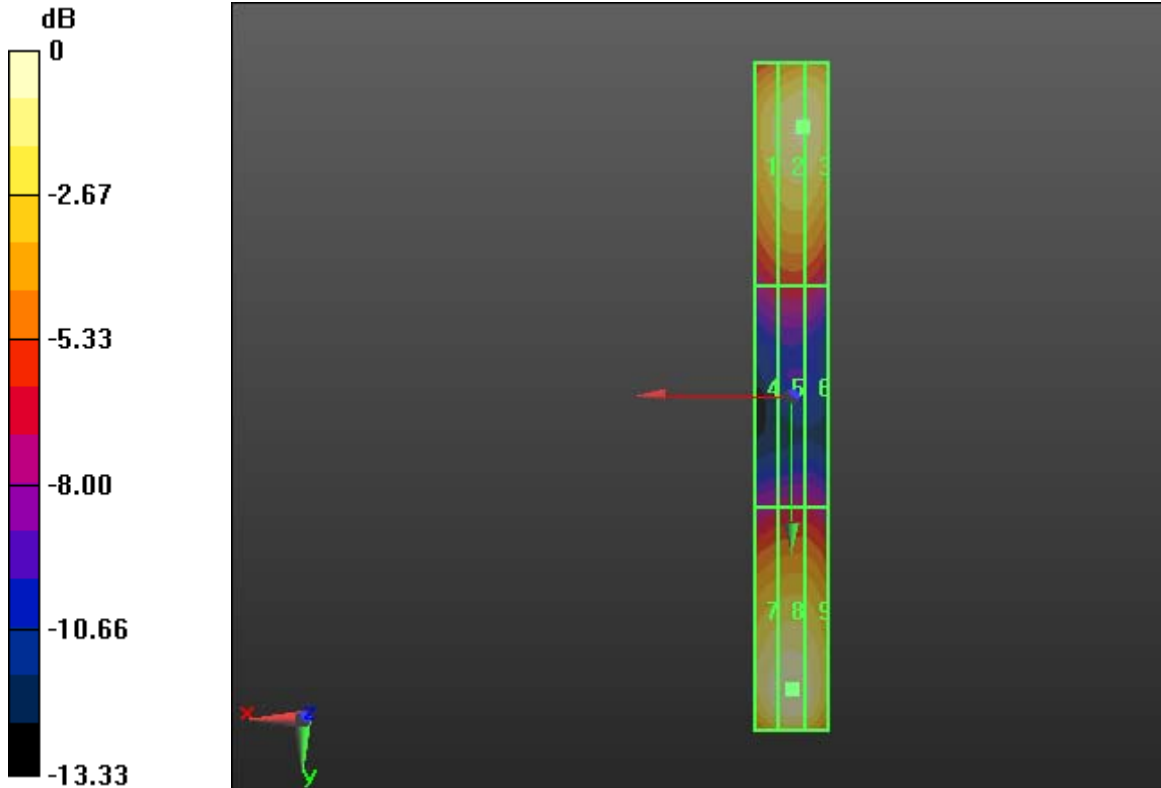
| | | |
|------------------|------------------|------------------|
| 162.8 V/m | 168.4 V/m | 161.7 V/m |
|------------------|------------------|------------------|

Cursor:


Total = 168.4 V/m

E Category: M4

Location: 0, 79, 4.7 mm



0 dB = 168.4V/m = 44.53 dB V/m

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Date/Time: 6/28/2012 1:13:34 PM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_PMF_GSM835 MHz_06_28_12

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: 1011

Communication System: GSM 835_PMF, Communication System: CW, Communication System: AM 80%; Frequency: 835 MHz
 Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³
 Phantom section: RF Section
 Measurement Standard: DASYS (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/9/2012
- Sensor-Surface: (Fix Surface), z = 4.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASYS2 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole E-Field measurement/E Scan - GSM 835_PMF/Hearing Aid Compatibility Test (41x361x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm
 Reference Value = 34.76 V/m; Power Drift = -0.00 dB
 PMR not calibrated. PMF = 1.000 is applied.
 E-field emissions = 54.25 V/m
Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

| | | |
|--------------------------------------|--------------------------------------|--------------------------------------|
| Grid 1 M4 49.26 V/m | Grid 2 M4 51.48 V/m | Grid 3 M4 51.48 V/m |
| Grid 4 M4 27.95 V/m | Grid 5 M4 28.56 V/m | Grid 6 M4 28.13 V/m |
| Grid 7 M4 51.48 V/m | Grid 8 M4 54.25 V/m | Grid 9 M4 53.95 V/m |



Author Data
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Cursor:

Total = 54.247 V/m
 E Category: M4
 Location: -2.5, 80.5, 4.7 mm

**Dipole E-Field measurement/E Scan - CW 835_PMF/Hearing Aid
 Compatibility Test (41x361x1):** Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm
 Reference Value = 103.0 V/m; Power Drift = -0.02 dB
 PMR not calibrated. PMF = 1.000 is applied.
 E-field emissions = 162.8 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

| | | |
|--------------------------------------|--------------------------------------|--------------------------------------|
| Grid 1 M4 148.5 V/m | Grid 2 M4 160.5 V/m | Grid 3 M4 160.4 V/m |
| Grid 4 M4 82.74 V/m | Grid 5 M4 86.24 V/m | Grid 6 M4 84.62 V/m |
| Grid 7 M4 158.1 V/m | Grid 8 M4 162.8 V/m | Grid 9 M4 155.2 V/m |

Cursor:

Total = 162.8 V/m
 E Category: M4
 Location: 0.5, 79.5, 4.7 mm

**Dipole E-Field measurement/E Scan - AM80%_ 835_PMF/Hearing
 Aid Compatibility Test (41x361x1):** Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm
 Reference Value = 64.73 V/m; Power Drift = 0.02 dB
 PMR not calibrated. PMF = 1.000 is applied.
 E-field emissions = 102.0 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

| | | |
|--------------------------------------|--------------------------------------|--------------------------------------|
| Grid 1 M4 93.30 V/m | Grid 2 M4 100.3 V/m | Grid 3 M4 100.3 V/m |
| Grid 4 M4 | Grid 5 M4 | Grid 6 M4 |

Author Data
Daoud Attayi

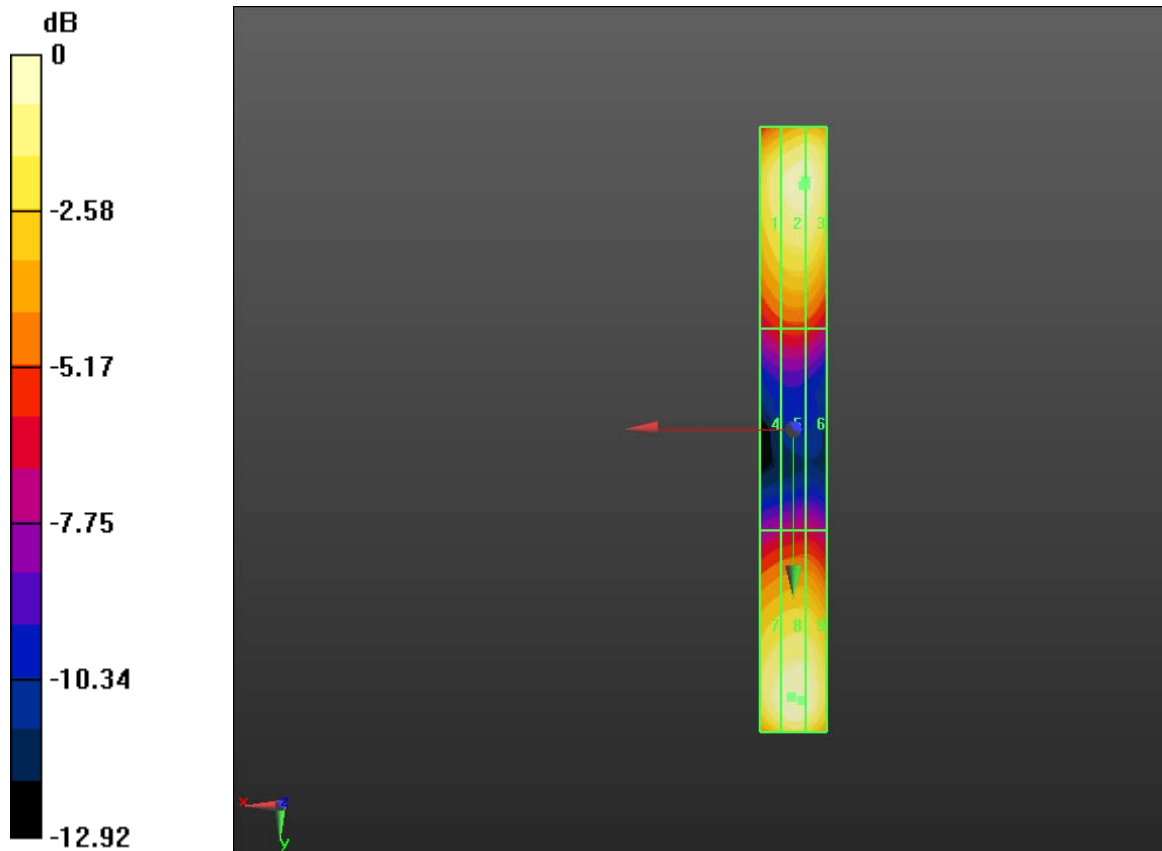
Dates of Test
Feb. 17, June 28, Dec. 17-18, 2012

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FCC ID
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| | | |
|------------------|------------------|------------------|
| 52.75 V/m | 54.62 V/m | 53.83 V/m |
| Grid 7 M4 | Grid 8 M4 | Grid 9 M4 |
| 99.38 V/m | 102.0 V/m | 97.92 V/m |

Cursor:
 Total = 102.0 V/m
 E Category: M4
 Location: 0.5, 79.5, 4.7 mm



0 dB = 54.250V/m = 34.69 dB V/m

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Date/Time: 2/17/2012 12:24:15 PM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_PMF_UMTS835 MHz_02_17_12

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: 1011

Communication System: WCDMA FDD V, Communication System: CW, Communication System: AM 80%; Frequency: 835 MHz

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASYS (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/9/2012
- Sensor-Surface: (Fix Surface), z = 4.7
- Electronics: DAE3 Sn472; Calibrated: 3/7/2011
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASYS2 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole E-Field measurement/E Scan - UMTS 835_PMF/Hearing Aid Compatibility Test (41x361x1):

Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 41.08 V/m; Power Drift = 0.03 dB

PMR not calibrated. PMF = 1.000 is applied.

E-field emissions = 64.41 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

| | | |
|--------------------------------------|--------------------------------------|--------------------------------------|
| Grid 1 M4 53.11 V/m | Grid 2 M4 55.59 V/m | Grid 3 M4 55.40 V/m |
| Grid 4 M4 29.72 V/m | Grid 5 M4 30.66 V/m | Grid 6 M4 29.79 V/m |
| Grid 7 M4 61.55 V/m | Grid 8 M4 64.41 V/m | Grid 9 M4 63.22 V/m |

Cursor:

Total = 64.412 V/m

E Category: M4

Location: -0.5, 79, 4.7 mm

**Dipole E-Field measurement/E Scan - CW 835_PMF/Hearing Aid
 Compatibility Test (41x361x1):** Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 43.11 V/m; Power Drift = -0.14 dB

PMR not calibrated. PMF = 1.000 is applied.

E-field emissions = 68.64 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

| | | |
|--------------------------------------|--------------------------------------|--------------------------------------|
| Grid 1 M4 58.55 V/m | Grid 2 M4 59.20 V/m | Grid 3 M4 57.13 V/m |
| Grid 4 M4 32.35 V/m | Grid 5 M4 32.63 V/m | Grid 6 M4 31.24 V/m |
| Grid 7 M4 61.85 V/m | Grid 8 M4 68.64 V/m | Grid 9 M4 68.56 V/m |



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Cursor:

Total = 68.635 V/m
E Category: M4
Location: -3, 79.5, 4.7 mm

**Dipole E-Field measurement/E Scan - AM80%_ 835_PMF/Hearing
Aid Compatibility Test (41x361x1):** Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm
Reference Value = 28.41 V/m; Power Drift = 0.09 dB
PMR not calibrated. PMF = 1.000 is applied.
E-field emissions = 45.21 V/m

Near-field category: **M4 (AWF 0 dB)**

PMF scaled E-field

| | | |
|--------------------------------------|--------------------------------------|--------------------------------------|
| Grid 1 M4 38.28 V/m | Grid 2 M4 38.73 V/m | Grid 3 M4 37.25 V/m |
| Grid 4 M4 21.72 V/m | Grid 5 M4 21.89 V/m | Grid 6 M4 20.80 V/m |
| Grid 7 M4 40.90 V/m | Grid 8 M4 45.21 V/m | Grid 9 M4 45.16 V/m |

Cursor:

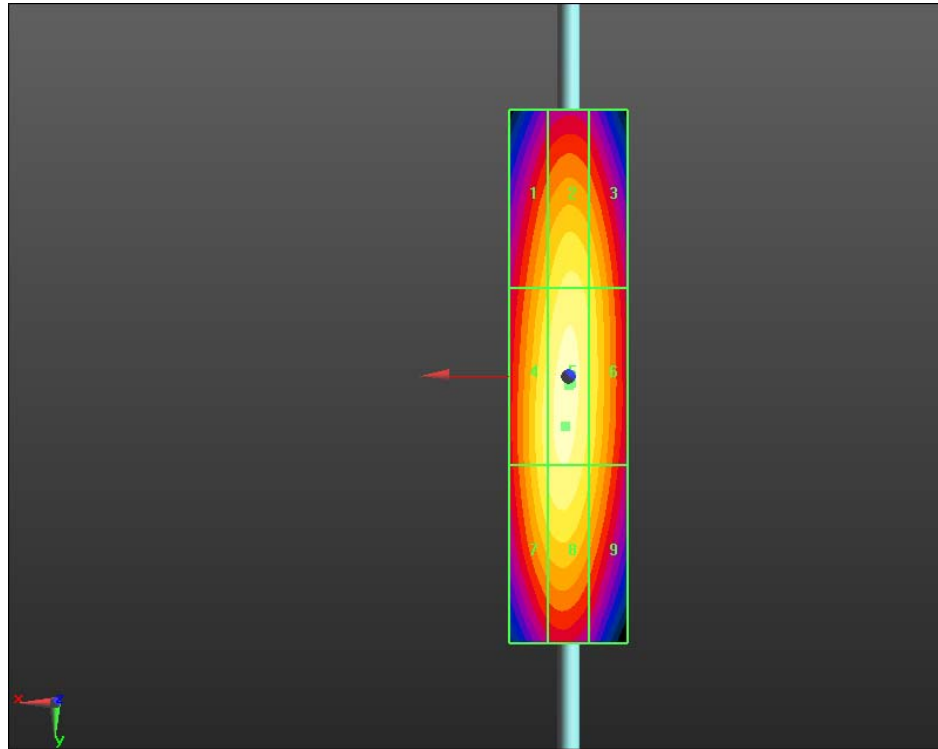
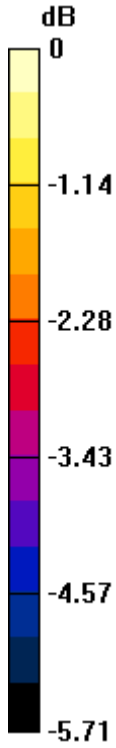
Total = 45.209 V/m
E Category: M4
Location: -3, 79.5, 4.7 mm

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0 dB = 0.180A/m = -14.89 dB A/m

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Date/Time: 12/17/2012 11:54:55 PM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_validation_1880 MHz_12_17_12

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: 1008

Communication System: CW; Frequency: 1880 MHz
Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³
Phantom section: RF Section
Measurement Standard: DASYS (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/9/2012
- Sensor-Surface: (Fix Surface), z = 4.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASYS2 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole E-Field measurement/E Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test

(41x181x1): Measurement grid: dx=5mm, dy=5mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 145.2 V/m; Power Drift = -0.03 dB
PMR not calibrated. PMF = 1.000 is applied.
E-field emissions = 128.6 V/m
Near-field category: M2 (AWF 0 dB)

PMF scaled E-field

| | | |
|--------------------------------------|--------------------------------------|--------------------------------------|
| Grid 1 M2 117.2 V/m | Grid 2 M2 123.0 V/m | Grid 3 M2 122.0 V/m |
| Grid 4 M3 87.82 V/m | Grid 5 M3 90.83 V/m | Grid 6 M3 89.07 V/m |
| Grid 7 M2 | Grid 8 M2 | Grid 9 M2 |

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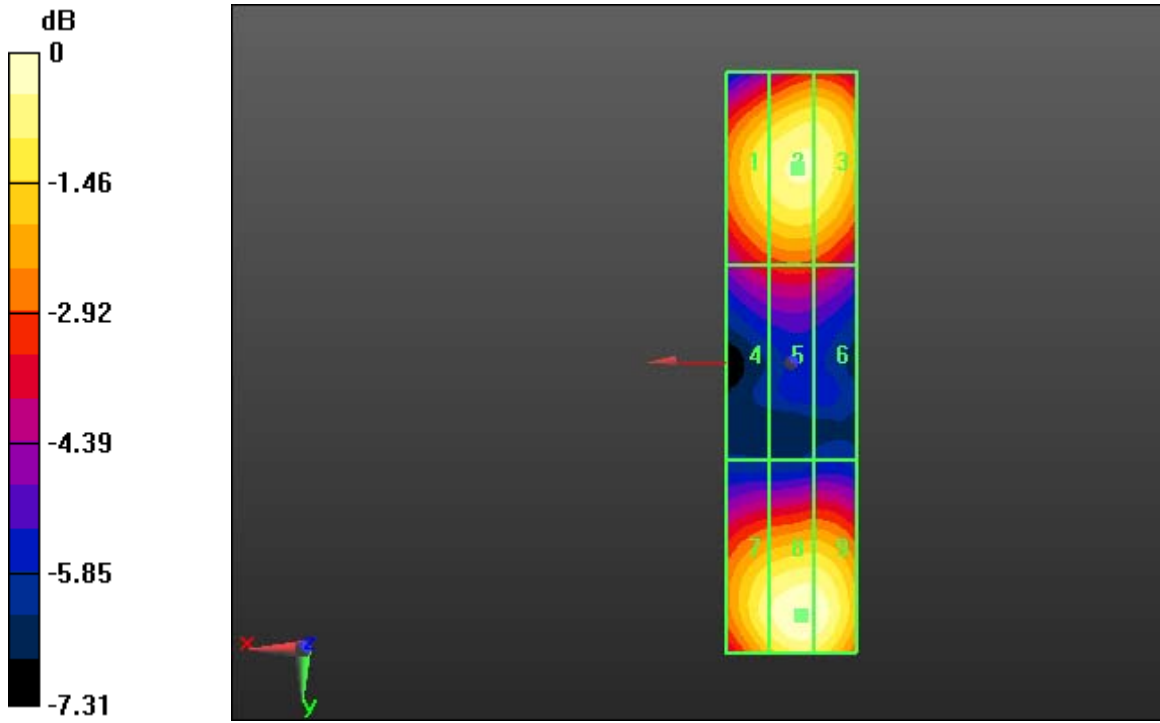
| | | |
|------------------|------------------|------------------|
| 120.5 V/m | 128.6 V/m | 127.6 V/m |
|------------------|------------------|------------------|

Cursor:


Total = 128.6 V/m

E Category: M2

Location: -1.5, 39, 4.7 mm



0 dB = 128.6V/m = 42.18 dB V/m

| | | | |
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Date/Time: 6/28/2012 12:54:33 PM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_PMF_GSM1880 MHz_06_28_12

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: 1008

Communication System: GSM 1880, Communication System: CW, Communication System: AM 80%; Frequency: 1880 MHz

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASYS (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/9/2012
- Sensor-Surface: (Fix Surface), z = 4.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASYS2 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole E-Field measurement/E Scan - GSM 1880_PMF/Hearing Aid Compatibility Test (41x181x1):

Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 33.26 V/m; Power Drift = 0.00 dB

PMR not calibrated. PMF = 1.000 is applied.

E-field emissions = 29.81 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

| | | |
|--------------------------------------|--------------------------------------|--------------------------------------|
| Grid 1 M4 27.34 V/m | Grid 2 M4 28.65 V/m | Grid 3 M4 28.59 V/m |
| Grid 4 M4 19.83 V/m | Grid 5 M4 20.51 V/m | Grid 6 M4 20.10 V/m |
| Grid 7 M4 28.20 V/m | Grid 8 M4 29.81 V/m | Grid 9 M4 29.37 V/m |



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Total = 29.810 V/m
 E Category: M4
 Location: -1, 38.5, 4.7 mm

**Dipole E-Field measurement/E Scan- CW 1800_PMF/Hearing Aid
 Compatibility Test (41x181x1):** Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm
 Reference Value = 95.34 V/m; Power Drift = 0.01 dB
 PMR not calibrated. PMF = 1.000 is applied.
 E-field emissions = 84.88 V/m

Near-field category: M3 (AWF 0 dB)

PMF scaled E-field

| | | |
|--------------------------------------|--------------------------------------|--------------------------------------|
| Grid 1 M3 78.80 V/m | Grid 2 M3 82.95 V/m | Grid 3 M3 82.43 V/m |
| Grid 4 M4 56.84 V/m | Grid 5 M4 58.53 V/m | Grid 6 M4 56.53 V/m |
| Grid 7 M3 80.11 V/m | Grid 8 M3 84.88 V/m | Grid 9 M3 83.31 V/m |

Cursor:

Total = 84.885 V/m
 E Category: M3
 Location: -0.5, 38.5, 4.7 mm

**Dipole E-Field measurement/E Scan - AM80%_ 1880_PMF/Hearing
 Aid Compatibility Test (41x181x1):** Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm
 Reference Value = 60.62 V/m; Power Drift = -0.03 dB
 PMR not calibrated. PMF = 1.000 is applied.
 E-field emissions = 53.60 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

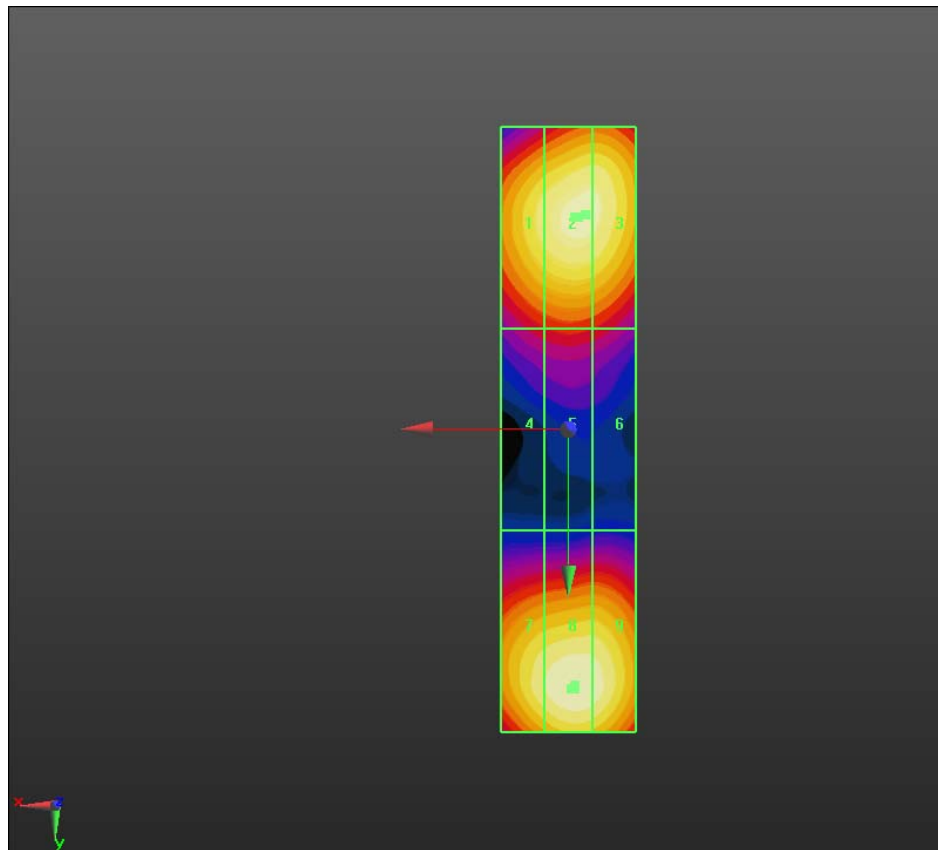
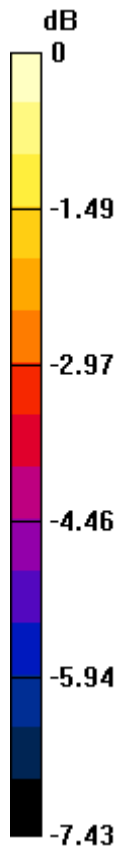
| | | |
|--------------------------------------|--------------------------------------|--------------------------------------|
| Grid 1 M4 49.75 V/m | Grid 2 M4 52.55 V/m | Grid 3 M4 52.06 V/m |
| Grid 4 M4 35.78 V/m | Grid 5 M4 36.92 V/m | Grid 6 M4 36.02 V/m |
| Grid 7 M4 50.66 V/m | Grid 8 M4 53.60 V/m | Grid 9 M4 52.63 V/m |

Cursor:


Total = 53.599 V/m

E Category: M4

Location: -1, 38, 4.7 mm



0 dB = 29.810V/m = 29.49 dB V/m

| | | | |
|---|---|--|--------------------------------------|
|  | Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFL111LW | | Page 29 (96) |
| | Author Data Daoud Attayi | Dates of Test Feb. 17, June 28, Dec. 17-18, 2012 | Report No RTS-6026-1302-03 |

Date/Time: 2/17/2012 2:20:23 PM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_PMF_UMTS1880 MHz_02_17_12

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: 1008

Communication System: WCDMA FDD II, Communication System: CW, Communication System: AM 80%; Frequency: 1880 MHz

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASYS (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/9/2012
- Sensor-Surface: (Fix Surface), z = 4.7
- Electronics: DAE3 Sn472; Calibrated: 3/7/2011
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASYS 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole E-Field measurement/E Scan - UMTS 1880_PMF/Hearing Aid Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 47.02 V/m; Power Drift = 0.01 dB

PMR not calibrated. PMF = 1.000 is applied.

E-field emissions = 42.43 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

| | | |
|--------------------------------------|--------------------------------------|--------------------------------------|
| Grid 1 M4 37.98 V/m | Grid 2 M4 39.42 V/m | Grid 3 M4 39.04 V/m |
| Grid 4 M4 26.86 V/m | Grid 5 M4 27.50 V/m | Grid 6 M4 26.70 V/m |
| Grid 7 M4 39.63 V/m | Grid 8 M4 42.43 V/m | Grid 9 M4 41.87 V/m |

Cursor:

Total = 42.427 V/m

E Category: M4

Location: -1, 38, 4.7 mm

**Dipole E-Field measurement/E Scan- CW 1800_PMF/Hearing Aid
 Compatibility Test (41x181x1):** Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 47.33 V/m; Power Drift = -0.05 dB

PMR not calibrated. PMF = 1.000 is applied.

E-field emissions = 42.41 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

| | | |
|--------------------------------------|--------------------------------------|--------------------------------------|
| Grid 1 M4 38.23 V/m | Grid 2 M4 39.51 V/m | Grid 3 M4 39.41 V/m |
| Grid 4 M4 26.94 V/m | Grid 5 M4 27.41 V/m | Grid 6 M4 26.77 V/m |
| Grid 7 M4 40.02 V/m | Grid 8 M4 42.41 V/m | Grid 9 M4 41.99 V/m |



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Cursor:

Total = 42.409 V/m
 E Category: M4
 Location: -1.5, 38, 4.7 mm

**Dipole E-Field measurement/E Scan - AM80%_ 1880_PMF/Hearing
 Aid Compatibility Test (41x181x1):** Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm
 Reference Value = 30.18 V/m; Power Drift = 0.06 dB
 PMR not calibrated. PMF = 1.000 is applied.
 E-field emissions = 27.40 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

| | | |
|--------------------------------------|--------------------------------------|--------------------------------------|
| Grid 1 M4 24.40 V/m | Grid 2 M4 25.26 V/m | Grid 3 M4 24.95 V/m |
| Grid 4 M4 17.20 V/m | Grid 5 M4 17.65 V/m | Grid 6 M4 17.12 V/m |
| Grid 7 M4 25.54 V/m | Grid 8 M4 27.40 V/m | Grid 9 M4 27.02 V/m |

Cursor:

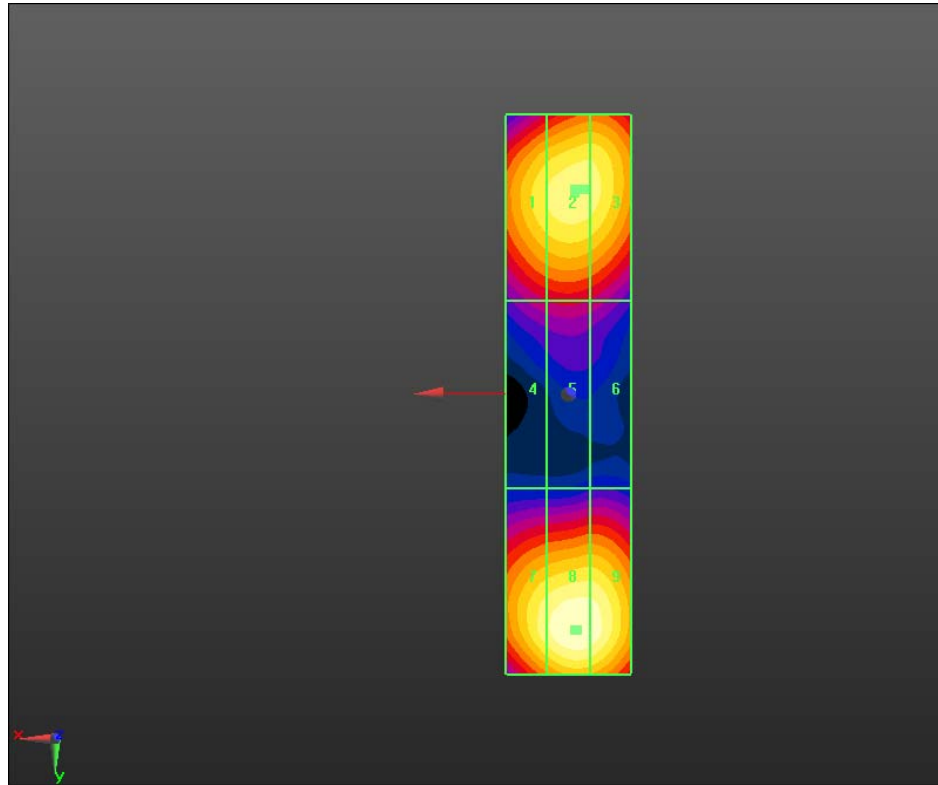
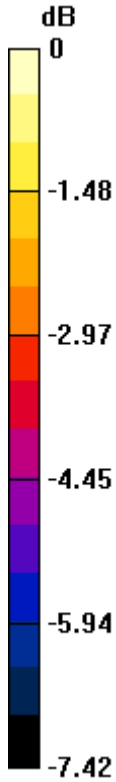
Total = 27.402 V/m
 E Category: M4
 Location: -1, 38, 4.7 mm

Author Data
Daoud Attayi


Dates of Test
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0 dB = 42.430V/m = 32.55 dB V/m

| | | | |
|---|--|--|--------------------------------------|
|  | Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFL111LW | | Page 33 (96) |
| | Author Data Daoud Attayi | Dates of Test Feb. 17, June 28, Dec. 17-18, 2012 | Report No RTS-6026-1302-03 |

Date/Time: 12/18/2012 12:59:09 PM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_validation_835 MHz_12_18_12

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: 1011

Communication System: CW; Frequency: 835 MHz
 Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³
 Phantom section: RF Section
 Measurement Standard: DASYS (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/9/2012
- Sensor-Surface: (Fix Surface), z = 4.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASYS 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole H-Field measurement with H3DV6 probe/H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid

Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm

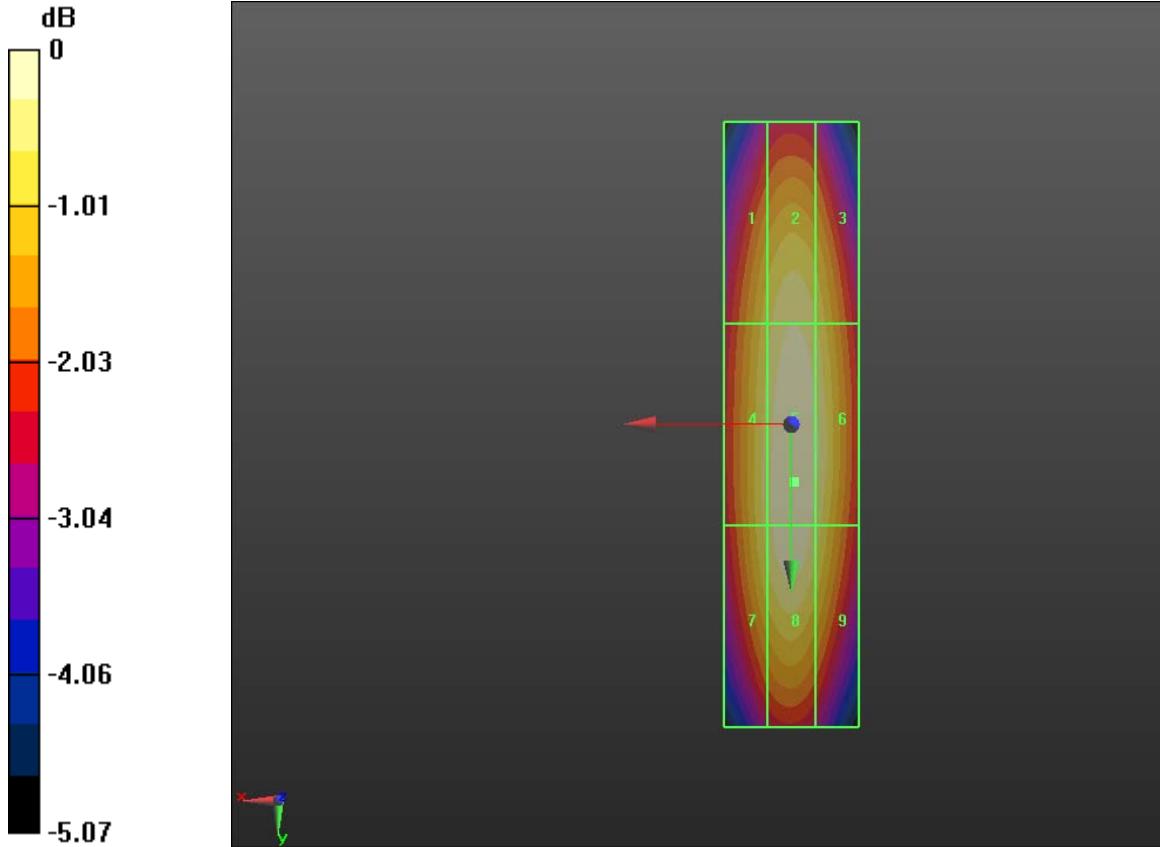
Device Reference Point: 0, 0, -6.3 mm
 Reference Value = 0.47 V/m; Power Drift = 0.10 dB
 PMR not calibrated. PMF = 1.000 is applied.
 H-field emissions = 0.44 A/m

Near-field category: M4 (AWF 0 dB)


PMF scaled H-field

| | | |
|-------------------------------------|-------------------------------------|-------------------------------------|
| Grid 1 M4 0.40 A/m | Grid 2 M4 0.42 A/m | Grid 3 M4 0.41 A/m |
| Grid 4 M4 0.42 A/m | Grid 5 M4 0.44 A/m | Grid 6 M4 0.43 A/m |
| Grid 7 M4 0.42 A/m | Grid 8 M4 0.44 A/m | Grid 9 M4 0.42 A/m |

Cursor:
 Total = 0.444 A/m
 H Category: M4
 Location: -0.5, 8.5, 4.7 mm



0 dB = 0.440A/m = -7.13 dB A/m

| | | | |
|---|--|--|--------------------------------------|
|  | Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFL111LW | | Page 35 (96) |
| | Author Data Daoud Attayi | Dates of Test Feb. 17, June 28, Dec. 17-18, 2012 | Report No RTS-6026-1302-03 |

Date/Time: 6/28/2012 11:48:13 AM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_PMF_GSM835 MHz_06_28_12

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: 1011

Communication System: GSM 835_PMF, Communication System: CW, Communication System: AM 80%; Frequency: 835 MHz
Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³
Phantom section: RF Section
Measurement Standard: DASYS (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/8/2011
- Sensor-Surface: (Fix Surface), z = 4.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASYS 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole H-Field measurement with H3DV6 probe/H Scan - GSM 835_PMF/Hearing Aid Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.17 V/m; Power Drift = -0.01 dB
PMR not calibrated. PMF = 1.000 is applied.
H-field emissions = 0.16 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

| | | |
|-------------------------------------|-------------------------------------|-------------------------------------|
| Grid 1 M4 0.15 A/m | Grid 2 M4 0.16 A/m | Grid 3 M4 0.15 A/m |
| Grid 4 M4 0.16 A/m | Grid 5 M4 0.16 A/m | Grid 6 M4 0.16 A/m |



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| | | |
|-------------------------------------|-------------------------------------|-------------------------------------|
| Grid 7 M4 0.15 A/m | Grid 8 M4 0.16 A/m | Grid 9 M4 0.15 A/m |
|-------------------------------------|-------------------------------------|-------------------------------------|

Cursor:

Total = 0.163 A/m
 H Category: M4
 Location: 0, 8.5, 4.7 mm

**Dipole H-Field measurement with H3DV6 probe/H Scan - CW
 835_PMF/Hearing Aid Compatibility Test (41x181x1):** Measurement grid:

dx=5mm, dy=5mm
 Device Reference Point: 0, 0, -6.3 mm
 Reference Value = 0.28 V/m; Power Drift = 0.08 dB
 PMR not calibrated. PMF = 1.000 is applied.
 H-field emissions = 0.47 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

| | | |
|-------------------------------------|-------------------------------------|-------------------------------------|
| Grid 1 M4 0.44 A/m | Grid 2 M4 0.46 A/m | Grid 3 M4 0.44 A/m |
| Grid 4 M4 0.45 A/m | Grid 5 M4 0.47 A/m | Grid 6 M4 0.45 A/m |
| Grid 7 M4 0.45 A/m | Grid 8 M4 0.47 A/m | Grid 9 M4 0.44 A/m |

Cursor:

Total = 0.471 A/m
 H Category: M4
 Location: 0, 8, 4.7 mm

**Dipole H-Field measurement with H3DV6 probe/H Scan -
 AM80%_PMF/Hearing Aid Compatibility Test (41x181x1):**

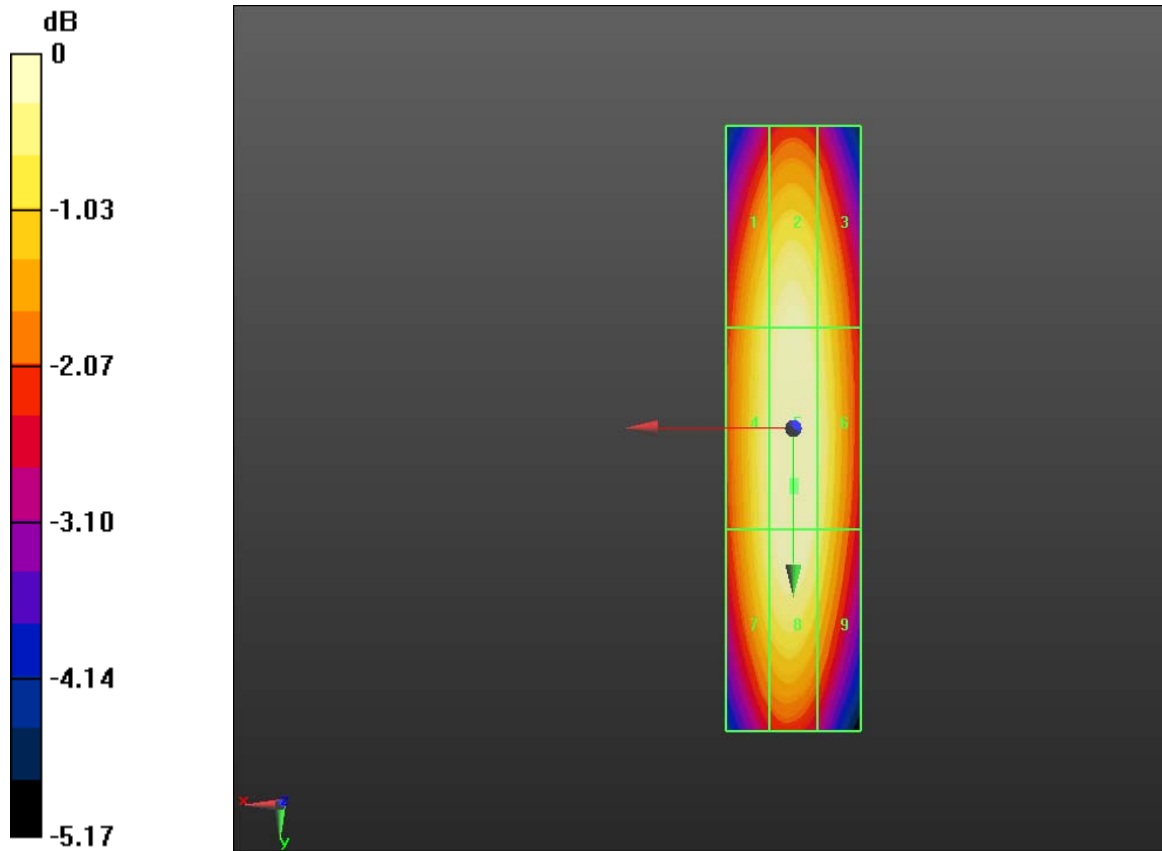
Measurement grid: dx=5mm, dy=5mm
 Device Reference Point: 0, 0, -6.3 mm
 Reference Value = 0.32 V/m; Power Drift = 0.12 dB
 PMR not calibrated. PMF = 1.000 is applied.
 H-field emissions = 0.30 A/m

Near-field category: M4 (AWF 0 dB)


PMF scaled H-field

| | | |
|-------------------------------------|-------------------------------------|-------------------------------------|
| Grid 1 M4 0.28 A/m | Grid 2 M4 0.29 A/m | Grid 3 M4 0.28 A/m |
| Grid 4 M4 0.29 A/m | Grid 5 M4 0.30 A/m | Grid 6 M4 0.29 A/m |
| Grid 7 M4 0.29 A/m | Grid 8 M4 0.30 A/m | Grid 9 M4 0.28 A/m |

Cursor:
 Total = 0.304 A/m
 H Category: M4
 Location: 0, 9, 4.7 mm



0 dB = 0.160A/m = -15.92 dB A/m

| | | | |
|---|--|--|--------------------------------------|
|  | Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFL111LW | | Page 38 (96) |
| | Author Data Daoud Attayi | Dates of Test Feb. 17, June 28, Dec. 17-18, 2012 | Report No RTS-6026-1302-03 |

Date/Time: 2/17/2012 4:08:25 PM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_PMF_UMTS835 MHz_02_17_12

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: 1011

Communication System: WCDMA FDD V, Communication System: CW, Communication System: AM 80%; Frequency: 835 MHz

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASYS (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/8/2011
- Sensor-Surface: (Fix Surface), z = 4.7
- Electronics: DAE3 Sn472; Calibrated: 3/7/2011
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASYS2 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole H-Field measurement with H3DV6 probe/H Scan - UMTS

835_PMF/Hearing Aid Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.19 V/m; Power Drift = 0.05 dB

PMR not calibrated. PMF = 1.000 is applied.

H-field emissions = 0.18 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

| | | |
|-------------------------------------|-------------------------------------|-------------------------------------|
| Grid 1 M4 0.16 A/m | Grid 2 M4 0.17 A/m | Grid 3 M4 0.16 A/m |
| Grid 4 M4 0.17 A/m | Grid 5 M4 0.18 A/m | Grid 6 M4 0.17 A/m |
| Grid 7 M4 0.17 A/m | Grid 8 M4 0.18 A/m | Grid 9 M4 0.17 A/m |

Cursor:

Total = 0.181 A/m

H Category: M4

Location: 0.5, 8.5, 4.7 mm

Dipole H-Field measurement with H3DV6 probe/H Scan - CW

835_PMF/Hearing Aid Compatibility Test (41x181x1): Measurement grid:

dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.11 V/m; Power Drift = 0.08 dB

PMR not calibrated. PMF = 1.000 is applied.

H-field emissions = 0.20 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

| | | |
|-------------------------------------|-------------------------------------|-------------------------------------|
| Grid 1 M4 0.17 A/m | Grid 2 M4 0.19 A/m | Grid 3 M4 0.18 A/m |
| Grid 4 M4 0.18 A/m | Grid 5 M4 0.20 A/m | Grid 6 M4 0.19 A/m |
| Grid 7 M4 0.18 A/m | Grid 8 M4 0.19 A/m | Grid 9 M4 0.18 A/m |



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Cursor:

Total = 0.197 A/m

H Category: M4

Location: -0.5, 1, 4.7 mm

**Dipole H-Field measurement with H3DV6 probe/H Scan -
AM80%_PMF/Hearing Aid Compatibility Test (41x181x1):**

Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.14 V/m; Power Drift = 0.10 dB

PMR not calibrated. PMF = 1.000 is applied.

H-field emissions = 0.13 A/m

Near-field category: **M4 (AWF 0 dB)**

PMF scaled H-field

| | | |
|-------------------------------------|-------------------------------------|-------------------------------------|
| Grid 1 M4 0.11 A/m | Grid 2 M4 0.12 A/m | Grid 3 M4 0.12 A/m |
| Grid 4 M4 0.12 A/m | Grid 5 M4 0.13 A/m | Grid 6 M4 0.12 A/m |
| Grid 7 M4 0.12 A/m | Grid 8 M4 0.12 A/m | Grid 9 M4 0.12 A/m |

Cursor:

Total = 0.127 A/m

H Category: M4

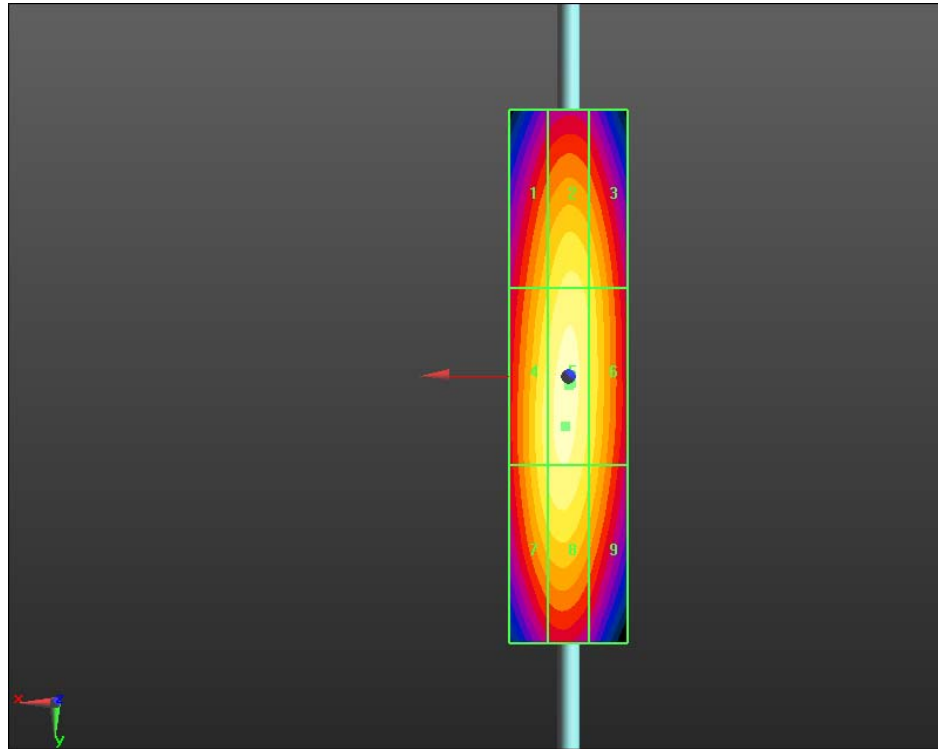
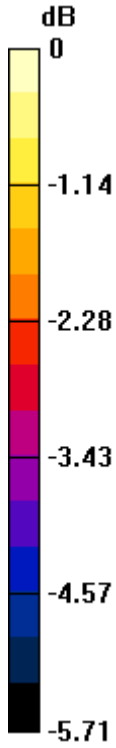
Location: 0, 1.5, 4.7 mm

Author Data
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Dates of Test
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0 dB = 0.180A/m = -14.89 dB A/m

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|  | Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFL111LW | | Page 42 (96) |
| | Author Data Daoud Attayi | Dates of Test Feb. 17, June 28, Dec. 17-18, 2012 | Report No RTS-6026-1302-03 |

Date/Time: 12/18/2012 1:06:37 PM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_validation_1880 MHz_12_18_12

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: 1008

Communication System: CW; Frequency: 1880 MHz
 Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³
 Phantom section: RF Section
 Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/9/2012
- Sensor-Surface: (Fix Surface), z = 4.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole H-Field measurement with H3DV6 probe/H Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid

Compatibility Test (41x101x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm
 Reference Value = 0.47 V/m; Power Drift = -0.04 dB
 PMF = 1.00 is applied.

H-field emissions = 0.446 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

| | | |
|--------------------------------------|--------------------------------------|--------------------------------------|
| Grid 1 M4 0.411 A/m | Grid 2 M4 0.429 A/m | Grid 3 M4 0.420 A/m |
| Grid 4 M4 0.429 A/m | Grid 5 M4 0.446 A/m | Grid 6 M4 0.429 A/m |
| Grid 7 M4 0.420 A/m | Grid 8 M4 0.438 A/m | Grid 9 M4 0.420 A/m |

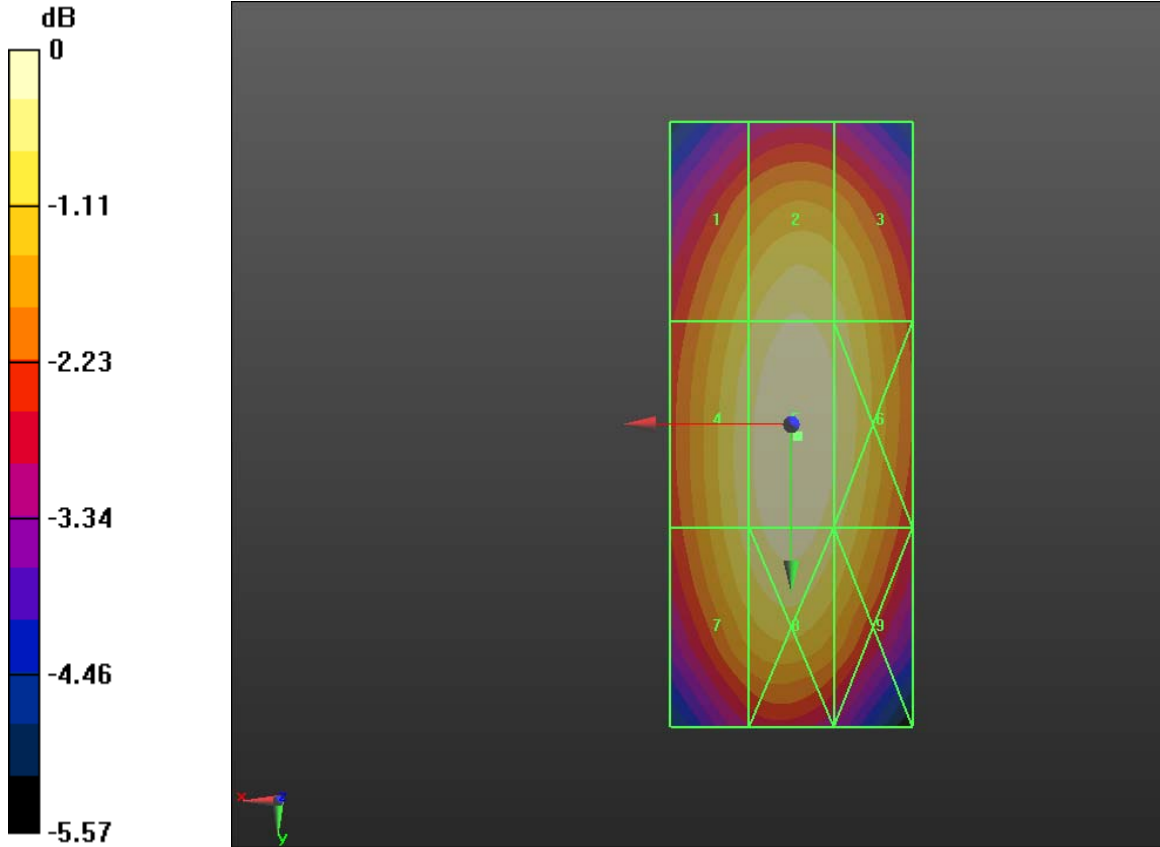
Author Data
Daoud Attayi

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RTS-6026-1302-03

FCC ID
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Cursor:
 Total = 0.446 A/m
 H Category: M4
 Location: -0.5, 1, 4.7 mm



0 dB = 0.446A/m = -7.01 dB A/m

| | | | |
|---|--|--|--------------------------------------|
|  | Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFL111LW | | Page 44 (96) |
| | Author Data Daoud Attayi | Dates of Test Feb. 17, June 28, Dec. 17-18, 2012 | Report No RTS-6026-1302-03 |

Date/Time: 6/28/2012 12:25:06 PM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_PMF_GSM1880 MHz_06_28_12

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: 1008

Communication System: GSM 1880_PMF, Communication System: CW, Communication System: AM 80%; Frequency: 1880 MHz
 Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³
 Phantom section: RF Section
 Measurement Standard: DASYS (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/8/2011
- Sensor-Surface: (Fix Surface), z = 4.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASYS 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole H-Field measurement with H3DV6 probe/H Scan -GSM 1880_PMF/Hearing Aid Compatibility Test (41x101x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm
 Reference Value = 0.11 V/m; Power Drift = -0.01 dB
 PMR not calibrated. PMF = 1.000 is applied.
 H-field emissions = 0.11 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

| | | |
|-------------------------------------|-------------------------------------|-------------------------------------|
| Grid 1 M4 0.10 A/m | Grid 2 M4 0.10 A/m | Grid 3 M4 0.10 A/m |
| Grid 4 M4 0.10 A/m | Grid 5 M4 0.11 A/m | Grid 6 M4 0.10 A/m |



| | | | |
|------------------------------------|--|--------------------------------------|------------------------------|
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|------------------------------------|--|--------------------------------------|------------------------------|

| | | |
|-------------------------------------|-------------------------------------|-------------------------------------|
| Grid 7 M4 0.10 A/m | Grid 8 M4 0.10 A/m | Grid 9 M4 0.10 A/m |
|-------------------------------------|-------------------------------------|-------------------------------------|

Cursor:
 Total = 0.105 A/m
 H Category: M4
 Location: 0, 0.5, 4.7 mm

**Dipole H-Field measurement with H3DV6 probe/H Scan - CW
 1800_PMF/Hearing Aid Compatibility Test (41x101x1):** Measurement

grid: dx=5mm, dy=5mm
 Device Reference Point: 0, 0, -6.3 mm
 Reference Value = 0.32 V/m; Power Drift = 0.00 dB
 PMR not calibrated. PMF = 1.000 is applied.
 H-field emissions = 0.30 A/m

Near-field category: M3 (AWF 0 dB)

PMF scaled H-field

| | | |
|-------------------------------------|-------------------------------------|-------------------------------------|
| Grid 1 M3 0.28 A/m | Grid 2 M3 0.29 A/m | Grid 3 M3 0.28 A/m |
| Grid 4 M3 0.29 A/m | Grid 5 M3 0.30 A/m | Grid 6 M3 0.29 A/m |
| Grid 7 M3 0.28 A/m | Grid 8 M3 0.29 A/m | Grid 9 M3 0.28 A/m |

Cursor:
 Total = 0.300 A/m
 H Category: M3
 Location: 0, 1, 4.7 mm

**Dipole H-Field measurement with H3DV6 probe/H Scan -
 AM80%_1880_PMF/Hearing Aid Compatibility Test (41x101x1):**

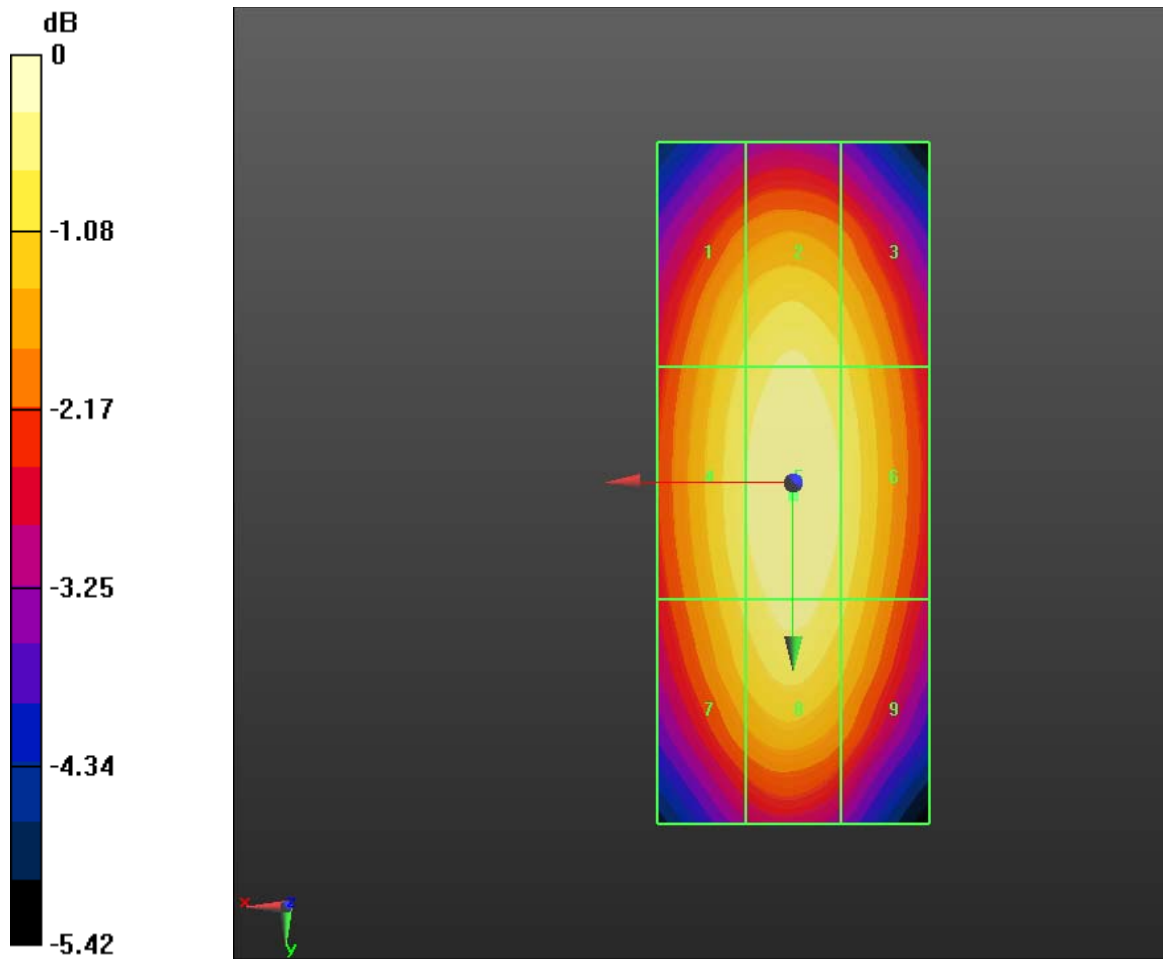
Measurement grid: dx=5mm, dy=5mm
 Device Reference Point: 0, 0, -6.3 mm
 Reference Value = 0.21 V/m; Power Drift = 0.02 dB
 PMR not calibrated. PMF = 1.000 is applied.
 H-field emissions = 0.19 A/m

Near-field category: M3 (AWF 0 dB)


PMF scaled H-field

| | | |
|-------------------------------------|-------------------------------------|-------------------------------------|
| Grid 1 M4 0.18 A/m | Grid 2 M4 0.19 A/m | Grid 3 M4 0.18 A/m |
| Grid 4 M4 0.19 A/m | Grid 5 M3 0.19 A/m | Grid 6 M4 0.19 A/m |
| Grid 7 M4 0.18 A/m | Grid 8 M3 0.19 A/m | Grid 9 M4 0.18 A/m |

Cursor:
 Total = 0.194 A/m
 H Category: M3
 Location: 0, 0.5, 4.7 mm



0 dB = 0.110A/m = -19.17 dB A/m

| | | | |
|---|---|--|--------------------------------------|
|  | Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFL111LW | | Page 47 (96) |
| | Author Data Daoud Attayi | Dates of Test Feb. 17, June 28, Dec. 17-18, 2012 | Report No RTS-6026-1302-03 |

Date/Time: 2/17/2012 3:56:44 PM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_PMF_UMTS1880 MHz_02_17_12

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: 1008

Communication System: WCDMA FDD II, Communication System: CW, Communication System: AM 80%; Frequency: 1880 MHz

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASYS (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/8/2011
- Sensor-Surface: (Fix Surface), z = 4.7
- Electronics: DAE3 Sn472; Calibrated: 3/7/2011
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASYS 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole H-Field measurement with H3DV6 probe/H Scan -UMTS

1880_PMF/Hearing Aid Compatibility Test (41x101x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.16 V/m; Power Drift = 0.06 dB

PMR not calibrated. PMF = 1.000 is applied.

H-field emissions = 0.15 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

| | | |
|-------------------------------------|-------------------------------------|-------------------------------------|
| Grid 1 M4 0.14 A/m | Grid 2 M4 0.14 A/m | Grid 3 M4 0.14 A/m |
| Grid 4 M4 0.14 A/m | Grid 5 M4 0.15 A/m | Grid 6 M4 0.14 A/m |
| Grid 7 M4 0.14 A/m | Grid 8 M4 0.15 A/m | Grid 9 M4 0.14 A/m |

Cursor:

Total = 0.150 A/m

H Category: M4

Location: 0, 0.5, 4.7 mm

**Dipole H-Field measurement with H3DV6 probe/H Scan - CW
 1880_PMF/Hearing Aid Compatibility Test (41x101x1): Measurement**

grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.16 V/m; Power Drift = -0.01 dB

PMR not calibrated. PMF = 1.000 is applied.

H-field emissions = 0.15 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

| | | |
|-------------------------------------|-------------------------------------|-------------------------------------|
| Grid 1 M4 0.14 A/m | Grid 2 M4 0.14 A/m | Grid 3 M4 0.14 A/m |
| Grid 4 M4 0.14 A/m | Grid 5 M4 0.15 A/m | Grid 6 M4 0.14 A/m |
| Grid 7 M4 0.14 A/m | Grid 8 M4 0.15 A/m | Grid 9 M4 0.14 A/m |



Author Data
Daoud Attayi

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Cursor:

Total = 0.149 A/m
 H Category: M4
 Location: 0, 0.5, 4.7 mm

**Dipole H-Field measurement with H3DV6 probe/H Scan -
 AM80%_1880_PMF/Hearing Aid Compatibility Test (41x101x1):**

Measurement grid: dx=5mm, dy=5mm
 Device Reference Point: 0, 0, -6.3 mm
 Reference Value = 0.10 V/m; Power Drift = -0.07 dB
 PMR not calibrated. PMF = 1.000 is applied.
 H-field emissions = 0.10 A/m

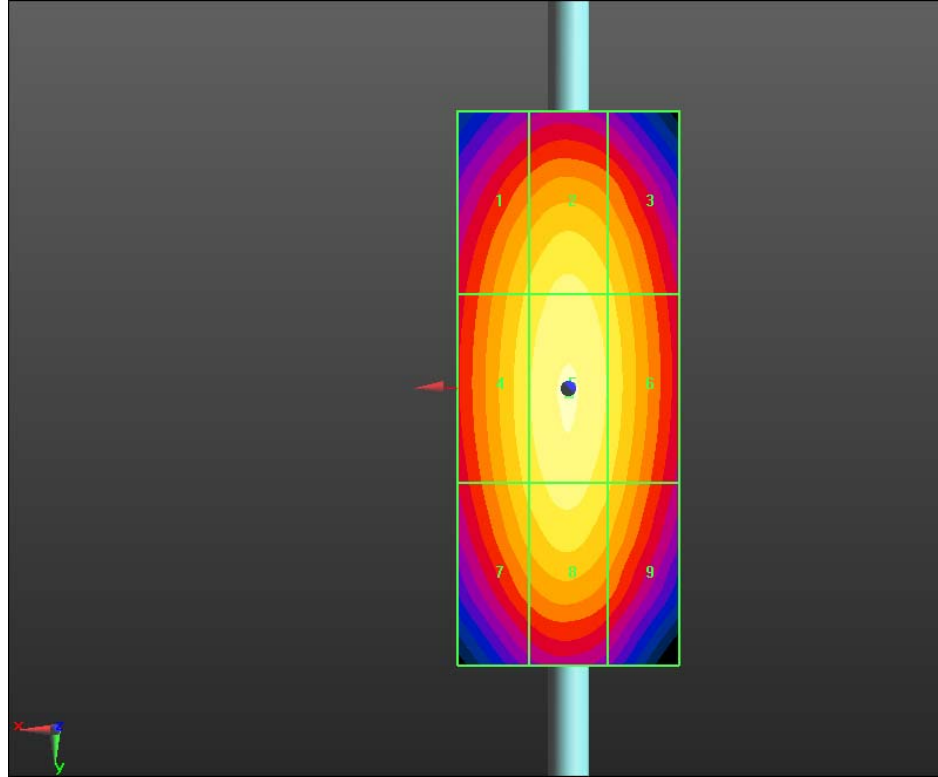
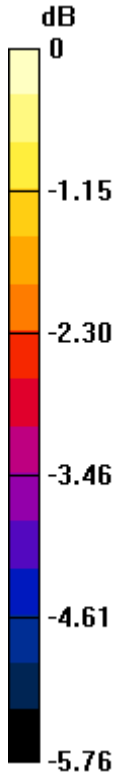
Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

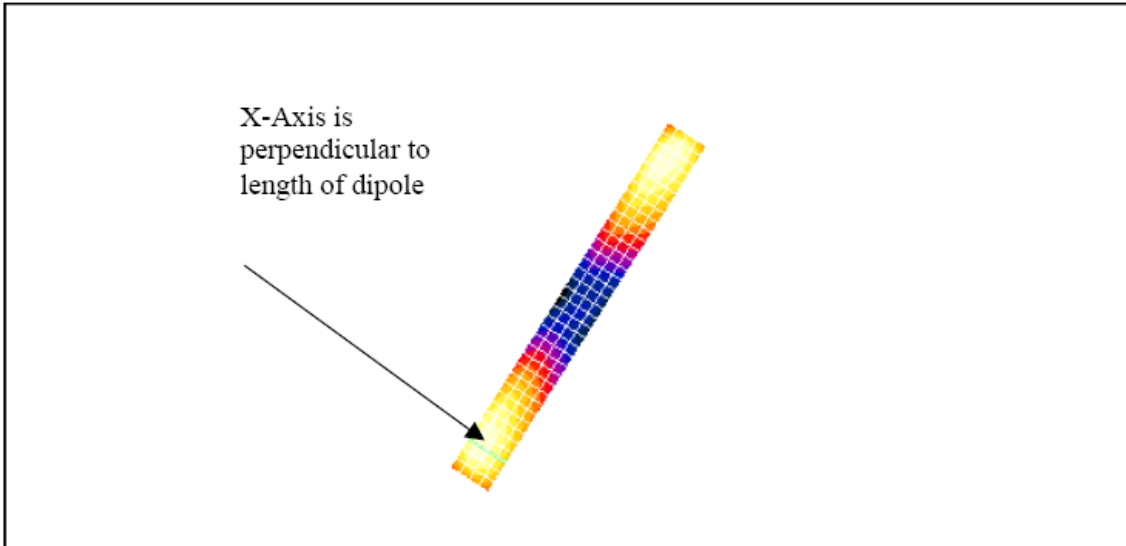
| | | |
|-------------------------------------|-------------------------------------|-------------------------------------|
| Grid 1 M4 0.09 A/m | Grid 2 M4 0.09 A/m | Grid 3 M4 0.09 A/m |
| Grid 4 M4 0.09 A/m | Grid 5 M4 0.10 A/m | Grid 6 M4 0.09 A/m |
| Grid 7 M4 0.09 A/m | Grid 8 M4 0.09 A/m | Grid 9 M4 0.09 A/m |

Cursor:

Total = 0.096 A/m
 H Category: M4
 Location: 0, 0, 4.7 mm



0 dB = 0.150A/m = -16.48 dB A/m



The green line in this figure shows the axis along which the points lie.

Comparison of 5mm and 2mm step sizes

An additional set of measurements was taken: dipole validations were performed using 5mm and 2mm step sizes. The delta between the two readings is insignificant for both field types (< 0.4% for E and 0% for H), demonstrating that 5mm is sufficient. The plots follow.



| | | | |
|------------------------------------|--|--------------------------------------|------------------------------|
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Date/Time: 14/07/2005 11:35:24 AM

Lab: RIM Testing Services (RTS)

Dipole Validation 1880 MHz_E-Field 07_14_05

DUT: HAC Dipole 1880 MHz; Type: CD1880V3

Communication System: CW; Frequency: 1880 MHz; Duty Cycle: 1:1
 Medium: Air Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³
 Phantom section: H Device Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2285; ConvF(1, 1, 1); Calibrated: 10/12/2004
- Sensor-Surface: 0mm (Fix Surface) Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 03/01/2005
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.5 Build 19; Postprocessing SW: SEMCAD, V1.8 Build 146

E Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (5x19x1):

Measurement grid: dx=5mm, dy=5mm
 Maximum value of Total (measured) = 134.8 V/m

E Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (41x181x1):

Measurement grid: dx=5mm, dy=5mm
 Maximum value of Total field (slot averaged) = 131.0 V/m

Hearing Aid Near-Field Category: M2 (AWF 0 dB)

E in V/m (Time averaged) E in V/m (Slot averaged)

| | | | | | |
|--------|--------|--------|--------|--------|--------|
| Grid 1 | Grid 2 | Grid 3 | Grid 1 | Grid 2 | Grid 3 |
| 123.2 | 138.1 | 138.4 | 123.2 | 138.1 | 138.4 |
| Grid 4 | Grid 5 | Grid 6 | Grid 4 | Grid 5 | Grid 6 |
| 80.9 | 92.3 | 92.2 | 80.9 | 92.3 | 92.2 |
| Grid 7 | Grid 8 | Grid 9 | Grid 7 | Grid 8 | Grid 9 |
| 119.8 | 131.0 | 130.7 | 119.8 | 131.0 | 130.7 |

| Category | AWF (dB) | Limits for E-Field Emissions (V/m) | Limits for H-Field Emissions (A/m) |
|----------|----------|------------------------------------|------------------------------------|
| M1 | 0 | 199.5 - 354.8 | 0.6 - 1.07 |
| | -5 | 149.6 - 266.1 | 0.45 - 0.8 |
| M2 | 0 | 112.2 - 199.5 | 0.34 - 0.6 |
| | -5 | 84.1 - 149.6 | 0.25 - 0.45 |
| M3 | 0 | 63.1 - 112.2 | 0.19 - 0.34 |
| | -5 | 47.3 - 84.1 | 0.15 - 0.25 |
| M4 | 0 | <63.1 | <0.19 |

file://C:\Program%20Files\DASY4\Print_Templates\Dipole%20Validation%201880%20... 14/07/2005



Author Data
Daoud Attayi

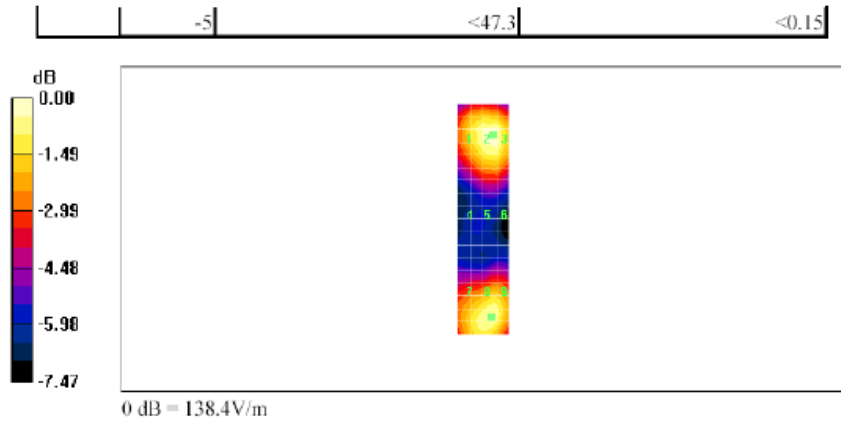
Dates of Test
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| | | | |
|------------------------------------|--|--------------------------------------|------------------------------|
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Lab: RIM Testing Services (RTS)

Dipole Validation 1880 MHz_2mm step_E-Field 07_14_05

DUT: HAC Dipole 1880 MHz; Type: CD1880V3

Communication System: CW; Frequency: 1880 MHz; Duty Cycle: 1:1
 Medium: Air Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³
 Phantom section: H Device Section

DASY4 Configuration:
 - Probe: ER3DV6 - SN2285; ConvF(1, 1, 1); Calibrated: 10/12/2004
 - Sensor-Surface: 0mm (Fix Surface) Sensor-Surface: (Fix Surface)
 - Electronics: DAE3 Sn472; Calibrated: 03/01/2005
 - Phantom: HAC Test Arch; Type: SD HAC P01 BA;
 - Measurement SW: DASY4, V4.5 Build 19; Postprocessing SW: SEMCAD, V1.8 Build 146

E Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (11x46x1):

Measurement grid: dx=2mm, dy=2mm
 Maximum value of Total (measured) = 138.0 V/m

E Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (101x451x1):

Measurement grid: dx=2mm, dy=2mm
 Maximum value of Total field (slot averaged) = 131.2 V/m

Hearing Aid Near-Field Category: M2 (AWF 0 dB)

| E in V/m (Time averaged) | | | E in V/m (Slot averaged) | | |
|--------------------------|--------------|--------------|--------------------------|--------------|--------------|
| Grid 1 | Grid 2 | Grid 3 | Grid 1 | Grid 2 | Grid 3 |
| 123.1 | 138.6 | 138.6 | 123.1 | 138.6 | 138.6 |
| Grid 4 | Grid 5 | Grid 6 | Grid 4 | Grid 5 | Grid 6 |
| 81.4 | 92.1 | 91.6 | 81.4 | 92.1 | 91.6 |
| Grid 7 | Grid 8 | Grid 9 | Grid 7 | Grid 8 | Grid 9 |
| 121.3 | 131.2 | 131.0 | 121.3 | 131.2 | 131.0 |

| Category | AWF (dB) | Limits for E-Field Emissions (V/m) | Limits for H-Field Emissions (A/m) |
|----------|----------|------------------------------------|------------------------------------|
| M1 | 0 | 199.5 - 354.8 | 0.6 - 1.07 |
| | -5 | 149.6 - 266.1 | 0.45 - 0.8 |
| M2 | 0 | 112.2 - 199.5 | 0.34 - 0.6 |
| | -5 | 84.1 - 149.6 | 0.25 - 0.45 |
| M3 | 0 | 63.1 - 112.2 | 0.19 - 0.34 |
| | -5 | 47.3 - 84.1 | 0.15 - 0.25 |
| M4 | 0 | <63.1 | <0.19 |

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Author Data
Daoud Attayi

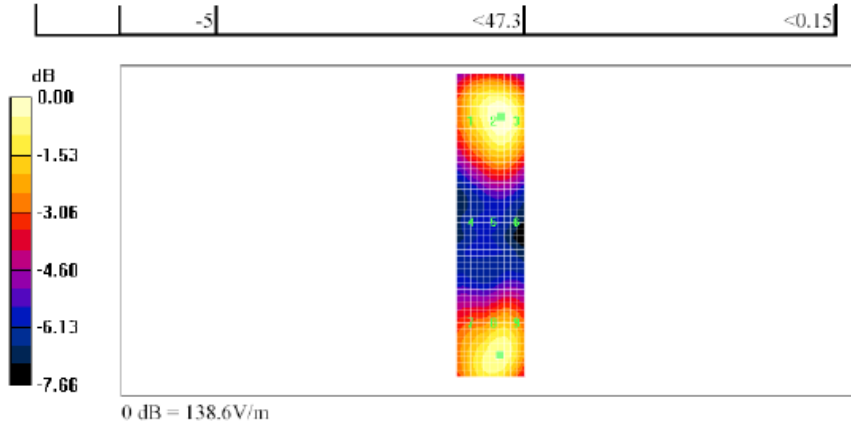
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Date/Time: 14/07/2005 12:43:02 PM

Lab: RIM Testing Services (RTS)

HAC_H_Dipole_CW 1880_5 mm step_07_14_05

DUT: HAC Dipole 1880 MHz; Type: CD1880V3

Communication System: CW; Frequency: 1880 MHz; Duty Cycle: 1:1
 Medium: Air Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³
 Phantom section: H Dipole Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 10/12/2004
- Sensor-Surface: 0mm (Fix Surface) Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 03/01/2005
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.5 Build 19; Postprocessing SW: SEMCAD, V1.8 Build 146

H Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (5x19x1):

Measurement grid: dx=5mm, dy=5mm
 Maximum value of Total (measured) = 0.406 A/m

H Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (41x181x1):

Measurement grid: dx=5mm, dy=5mm
 Maximum value of Total field (slot averaged) = 0.406 A/m

Hearing Aid Near-Field Category: M2 (AWF 0 dB)

H in A/m (Time averaged) H in A/m (Slot averaged)

| | | | | | |
|--------------|--------------|--------------|--------------|--------------|--------------|
| Grid 1 | Grid 2 | Grid 3 | Grid 1 | Grid 2 | Grid 3 |
| 0.342 | 0.359 | 0.344 | 0.342 | 0.359 | 0.344 |
| Grid 4 | Grid 5 | Grid 6 | Grid 4 | Grid 5 | Grid 6 |
| 0.389 | 0.406 | 0.389 | 0.389 | 0.406 | 0.389 |
| Grid 7 | Grid 8 | Grid 9 | Grid 7 | Grid 8 | Grid 9 |
| 0.363 | 0.378 | 0.363 | 0.363 | 0.378 | 0.363 |

| Category | AWF (dB) | Limits for E-Field Emissions (V/m) | Limits for H-Field Emissions (A/m) |
|----------|----------|------------------------------------|------------------------------------|
| M1 | 0 | 199.5 - 354.8 | 0.6 - 1.07 |
| | -5 | 149.6 - 266.1 | 0.45 - 0.8 |
| M2 | 0 | 112.2 - 199.5 | 0.34 - 0.6 |
| | -5 | 84.1 - 149.6 | 0.25 - 0.45 |
| M3 | 0 | 63.1 - 112.2 | 0.19 - 0.34 |
| | -5 | 47.3 - 84.1 | 0.15 - 0.25 |
| M4 | 0 | <63.1 | <0.19 |



Author Data
Daoud Attayi

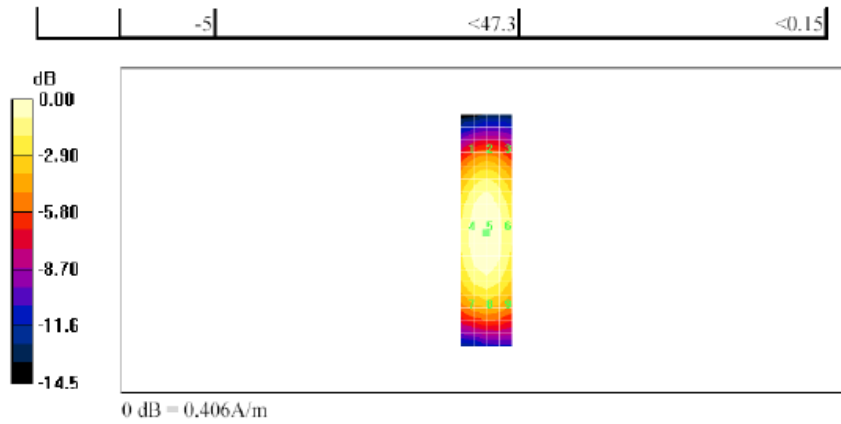
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FCC ID
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| | | | |
|------------------------------------|--|--------------------------------------|------------------------------|
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Lab: RIM Testing Services (RTS)

HAC_H_Dipole_CW 1880_2 mm step_07_14_05

DUT: HAC Dipole 1880 MHz; Type: CD1880V3

Communication System: CW; Frequency: 1880 MHz; Duty Cycle: 1:1
 Medium: Air Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³
 Phantom section: H Dipole Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 10/12/2004
- Sensor-Surface: 0mm (Fix Surface) Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 03/01/2005
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.5 Build 19; Postprocessing SW: SEMCAD, V1.8 Build 146

H Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (11x46x1):

Measurement grid: dx=2mm, dy=2mm
 Maximum value of Total (measured) = 0.406 A/m

H Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (101x451x1):

Measurement grid: dx=2mm, dy=2mm
 Maximum value of Total field (slot averaged) = 0.406 A/m

Hearing Aid Near-Field Category: M2 (AWF 0 dB)

H in A/m (Time averaged) H in A/m (Slot averaged)

| | | | | | |
|--------------|--------------|--------------|--------------|--------------|--------------|
| Grid 1 | Grid 2 | Grid 3 | Grid 1 | Grid 2 | Grid 3 |
| 0.347 | 0.361 | 0.348 | 0.347 | 0.361 | 0.348 |
| Grid 4 | Grid 5 | Grid 6 | Grid 4 | Grid 5 | Grid 6 |
| 0.394 | 0.406 | 0.391 | 0.394 | 0.406 | 0.391 |
| Grid 7 | Grid 8 | Grid 9 | Grid 7 | Grid 8 | Grid 9 |
| 0.367 | 0.380 | 0.365 | 0.367 | 0.380 | 0.365 |

| Category | AWF (dB) | Limits for E-Field Emissions (V/m) | Limits for H-Field Emissions (A/m) |
|----------|----------|------------------------------------|------------------------------------|
| M1 | 0 | 199.5 - 354.8 | 0.6 - 1.07 |
| | -5 | 149.6 - 266.1 | 0.45 - 0.8 |
| M2 | 0 | 112.2 - 199.5 | 0.34 - 0.6 |
| | -5 | 84.1 - 149.6 | 0.25 - 0.45 |
| M3 | 0 | 63.1 - 112.2 | 0.19 - 0.34 |
| | -5 | 47.3 - 84.1 | 0.15 - 0.25 |
| M4 | 0 | <63.1 | <0.19 |

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Author Data
Daoud Attayi

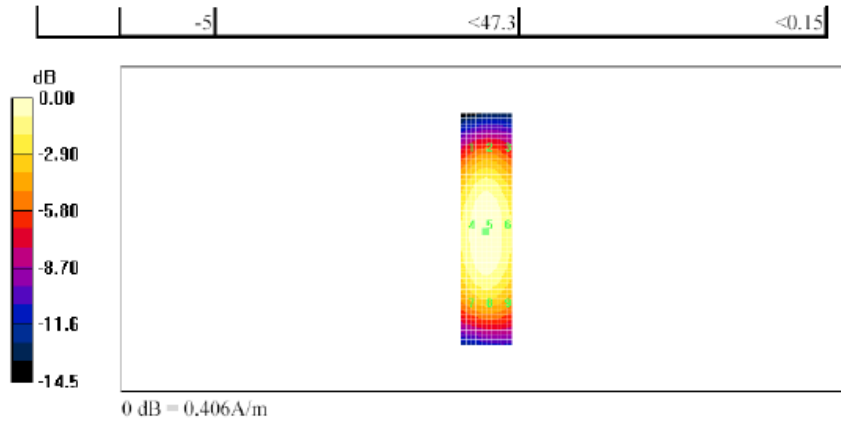
Dates of Test
Feb. 17, June 28, Dec. 17-18, 2012

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Document
**Annex A to Hearing Aid Compatibility RF Emissions Test
Report for the BlackBerry® Smartphone model RFL111LW**

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A.3 RF emission field plots

| | | | |
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|  | Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFL111LW | | Page 61 (96) |
| | Author Data Daoud Attayi | Dates of Test Feb. 17, June 28, Dec. 17-18, 2012 | Report No RTS-6026-1302-03 |

Date/Time: 12/18/2012 2:22:34 AM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_GSM850

DUT: BlackBerry Smartphone; Type: Sample ; Serial: 25CF0AD9

Communication System: GSM 850; Frequency: 824.2 MHz, Frequency: 836.8 MHz, Frequency: 848.8 MHz

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASYS (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/9/2012
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASYS2 52.8.0(692); SEMCAD X 14.6.4(4989)

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to Device_Low_Chan/Hearing Aid Compatibility Test

(101x101x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 90.20 V/m; Power Drift = -0.01 dB

PMR not calibrated. PMF = 3.000 is applied.

E-field emissions = 226.1 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

| | | |
|--------------------------------------|--------------------------------------|--------------------------------------|
| Grid 1 M3 194.7 V/m | Grid 2 M3 219.1 V/m | Grid 3 M3 218.1 V/m |
| Grid 4 M3 196.9 V/m | Grid 5 M3 226.1 V/m | Grid 6 M3 225.1 V/m |

| | | |
|--------------------------------------|--------------------------------------|--------------------------------------|
| Grid 7 M3 196.0 V/m | Grid 8 M3 223.9 V/m | Grid 9 M3 222.0 V/m |
|--------------------------------------|--------------------------------------|--------------------------------------|

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device_Mid_Chan/Hearing Aid

Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm
 Reference Value = 89.43 V/m; Power Drift = 0.03 dB
 PMR not calibrated. PMF = 3.000 is applied.
 E-field emissions = 230.7 V/m

Near-field category: **M3 (AWF -5 dB)**

PMF scaled E-field

| | | |
|--------------------------------------|--------------------------------------|--------------------------------------|
| Grid 1 M3 184.5 V/m | Grid 2 M3 219.1 V/m | Grid 3 M3 218.9 V/m |
| Grid 4 M3 192.4 V/m | Grid 5 M3 230.7 V/m | Grid 6 M3 230.4 V/m |
| Grid 7 M3 198.6 V/m | Grid 8 M3 230.4 V/m | Grid 9 M3 230.0 V/m |

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device_High_Chan/Hearing Aid

Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

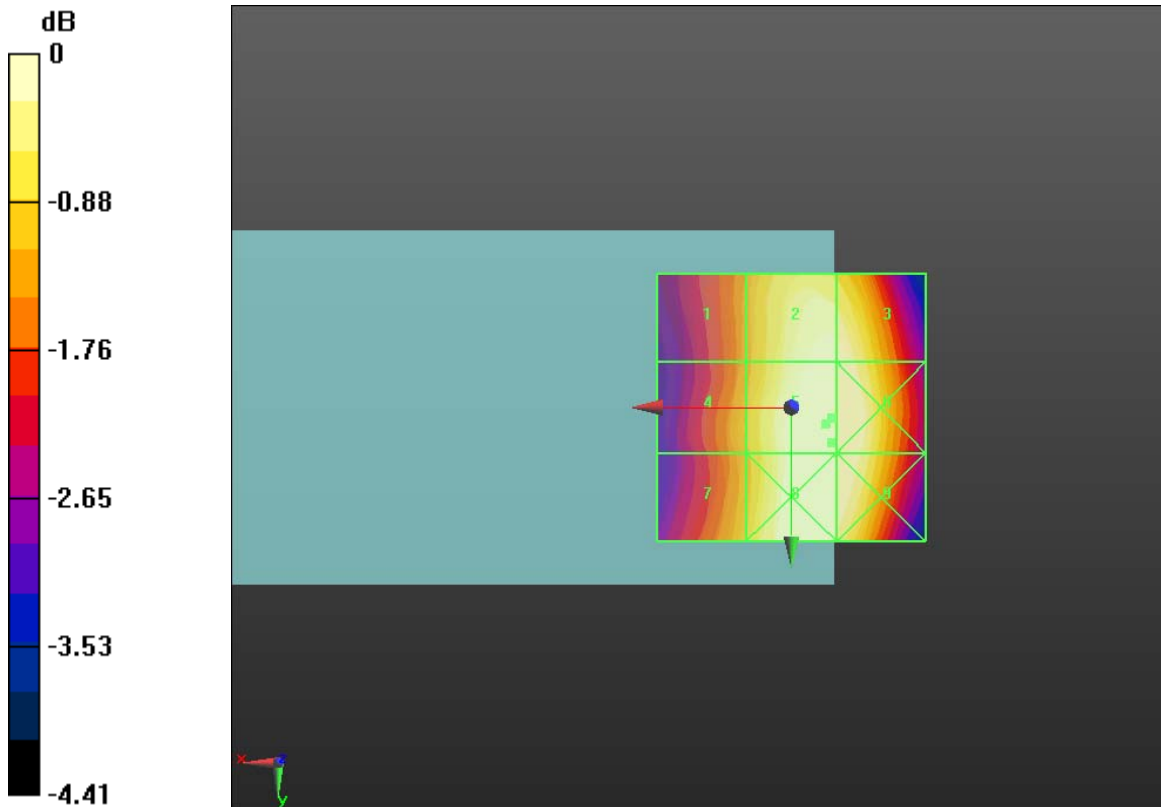
Device Reference Point: 0, 0, -6.3 mm
 Reference Value = 84.58 V/m; Power Drift = -0.08 dB
 PMR not calibrated. PMF = 3.000 is applied.
 E-field emissions = 212.9 V/m

Near-field category: **M3 (AWF -5 dB)**


PMF scaled E-field

| | | |
|--------------------------------------|--------------------------------------|--------------------------------------|
| Grid 1 M3 174.6 V/m | Grid 2 M3 205.9 V/m | Grid 3 M3 205.9 V/m |
| Grid 4 M3 | Grid 5 M3 | Grid 6 M3 |

| | | |
|--------------------------------------|--------------------------------------|--------------------------------------|
| 179.4 V/m | 212.9 V/m | 212.7 V/m |
| Grid 7 M3 182.2 V/m | Grid 8 M3 211.9 V/m | Grid 9 M3 211.2 V/m |



0 dB = 217.1V/m = 46.73 dB V/m

| | | | |
|---|--|--|--------------------------------------|
|  | Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFL111LW | | Page 64 (96) |
| | Author Data Daoud Attayi | Dates of Test Feb. 17, June 28, Dec. 17-18, 2012 | Report No RTS-6026-1302-03 |

Date/Time: 12/18/2012 9:57:48 PM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_GSM850_Telecoil

DUT: BlackBerry Smartphone; Type: Sample ; Serial: 25CF0AD9

Communication System: GSM 850; Frequency: 836.8 MHz
Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³
Phantom section: RF Section
Measurement Standard: DASYS (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/9/2012
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASYS2 52.8.0(692); SEMCAD X 14.6.4(4989)

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device_telecoil/Hearing Aid Compatibility Test (101x101x1):

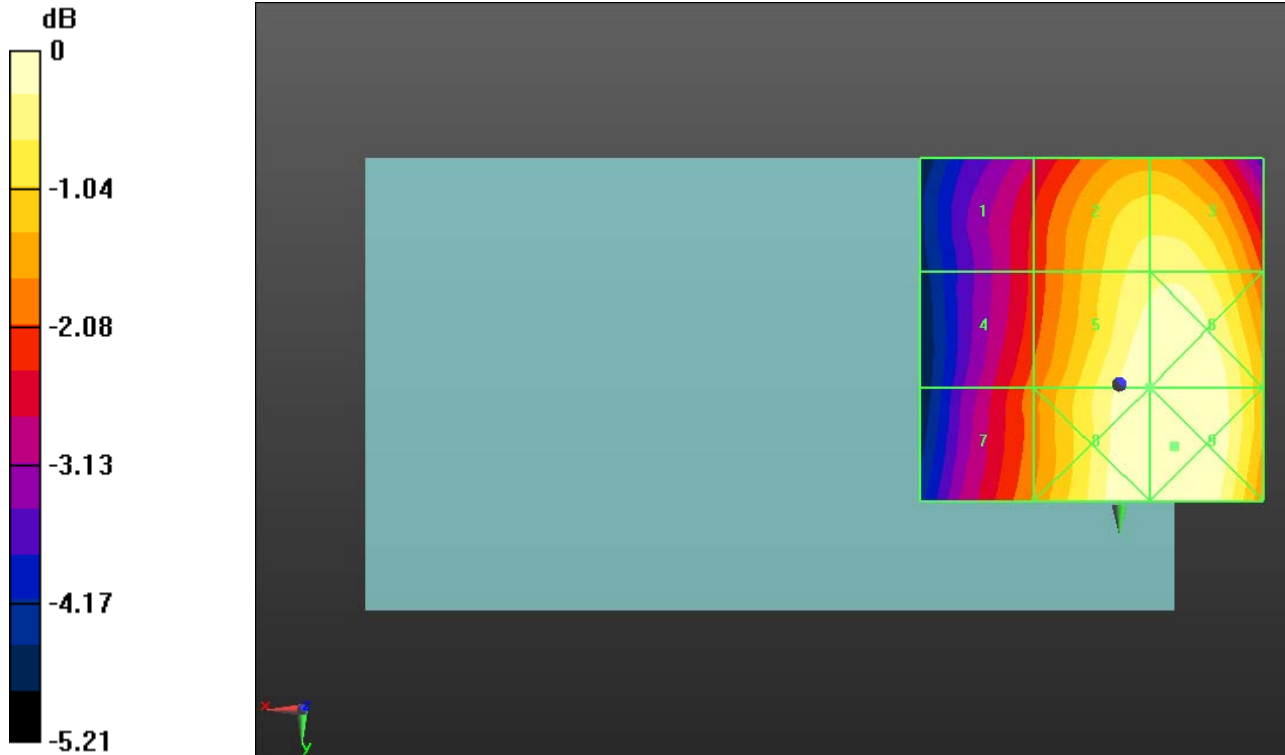
Measurement grid: dx=5mm, dy=5mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 85.88 V/m; Power Drift = -0.08 dB
PMR not calibrated. PMF = 3.000 is applied.
E-field emissions = 217.7 V/m

Near-field category: M3 (AWF -5 dB)


PMF scaled E-field

| | | |
|--------------------------------------|--------------------------------------|--------------------------------------|
| Grid 1 M3 164.6 V/m | Grid 2 M3 203.7 V/m | Grid 3 M3 204.8 V/m |
| Grid 4 M3 172.6 V/m | Grid 5 M3 217.7 V/m | Grid 6 M3 220.7 V/m |
| Grid 7 M3 | Grid 8 M3 | Grid 9 M3 |

177.1 V/m **221.6 V/m** **223.6 V/m**



0 dB = 214.8V/m = 46.64 dB V/m

| | | | |
|---|---|--|--------------------------------------|
|  | Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFL111LW | | Page 66 (96) |
| | Author Data Daoud Attayi | Dates of Test Feb. 17, June 28, Dec. 17-18, 2012 | Report No RTS-6026-1302-03 |

Date/Time: 12/18/2012 3:13:16 AM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_UMTS_Band_V

DUT: BlackBerry Smartphone; Type: Sample ; Serial: 25CF0AD9

Communication System: WCDMA FDD V; Frequency: 826.4 MHz, Frequency: 836.4 MHz, Frequency: 846.6 MHz
Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³
Phantom section: RF Section
Measurement Standard: DASYS (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/9/2012
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASYS2 52.8.0(692); SEMCAD X 14.6.4(4989)

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to Device_Low_Chan/Hearing Aid Compatibility Test

(101x101x1): Measurement grid: dx=5mm, dy=5mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 74.08 V/m; Power Drift = 0.09 dB
PMR not calibrated. PMF = 1.070 is applied.
E-field emissions = 66.01 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

| | | |
|--------------------------------------|--------------------------------------|--------------------------------------|
| Grid 1 M4 58.85 V/m | Grid 2 M4 65.32 V/m | Grid 3 M4 65.33 V/m |
| Grid 4 M4 57.72 V/m | Grid 5 M4 66.01 V/m | Grid 6 M4 66.01 V/m |

| | | |
|--------------------------------------|--------------------------------------|--------------------------------------|
| Grid 7 M4 56.79 V/m | Grid 8 M4 64.64 V/m | Grid 9 M4 64.64 V/m |
|--------------------------------------|--------------------------------------|--------------------------------------|

Cursor:
 Total = 66.014 V/m
 E Category: M4
 Location: -8.5, -0.5, 8.7 mm

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device_Mid_Chan/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm
 Device Reference Point: 0, 0, -6.3 mm
 Reference Value = 80.46 V/m; Power Drift = -0.07 dB
 PMR not calibrated. PMF = 1.070 is applied.
 E-field emissions = 72.82 V/m
Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

| | | |
|--------------------------------------|--------------------------------------|--------------------------------------|
| Grid 1 M4 61.67 V/m | Grid 2 M4 70.80 V/m | Grid 3 M4 70.74 V/m |
| Grid 4 M4 61.29 V/m | Grid 5 M4 72.82 V/m | Grid 6 M4 72.75 V/m |
| Grid 7 M4 60.71 V/m | Grid 8 M4 72.25 V/m | Grid 9 M4 72.16 V/m |

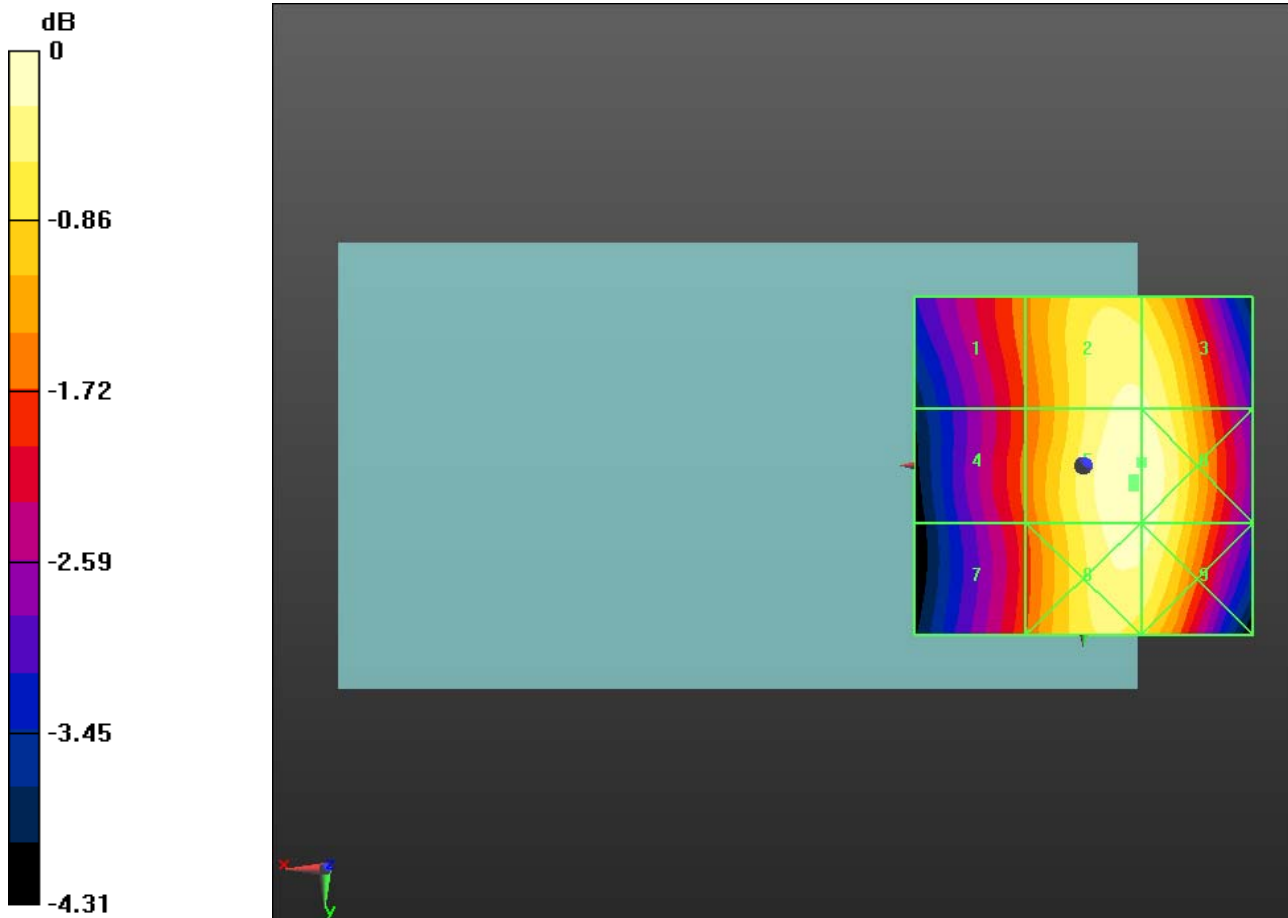
Cursor:
 Total = 72.817 V/m
 E Category: M4
 Location: -7.5, 3, 8.7 mm

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device_High_Chan/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm
 Device Reference Point: 0, 0, -6.3 mm
 Reference Value = 91.96 V/m; Power Drift = -0.06 dB
 PMR not calibrated. PMF = 1.070 is applied.
 E-field emissions = 82.86 V/m
Near-field category: M4 (AWF 0 dB)


PMF scaled E-field

| | | |
|--------------------------------------|--------------------------------------|--------------------------------------|
| Grid 1 M4 70.14 V/m | Grid 2 M4 80.95 V/m | Grid 3 M4 80.84 V/m |
| Grid 4 M4 69.50 V/m | Grid 5 M4 82.86 V/m | Grid 6 M4 82.79 V/m |
| Grid 7 M4 68.39 V/m | Grid 8 M4 81.91 V/m | Grid 9 M4 81.74 V/m |

Cursor:
 Total = 82.860 V/m
 E Category: M4
 Location: -7.5, 2, 8.7 mm



0 dB = 66.010V/m = 36.39 dB V/m

| | | | |
|---|--|--|--------------------------------------|
|  | Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFL111LW | | Page 69 (96) |
| | Author Data Daoud Attayi | Dates of Test Feb. 17, June 28, Dec. 17-18, 2012 | Report No RTS-6026-1302-03 |

Date/Time: 12/18/2012 9:18:12 PM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_GSM1900

DUT: BlackBerry Smartphone; Type: Sample ; Serial: 25CF0AD9

Communication System: GSM 1900; Frequency: 1850.2 MHz, Frequency: 1880 MHz, Frequency: 1909.8 MHz
Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³
Phantom section: RF Section
Measurement Standard: DASYS (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/9/2012
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASYS2 52.8.0(692); SEMCAD X 14.6.4(4989)

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to Device_Low_Chan/Hearing Aid Compatibility Test

(101x101x1): Measurement grid: dx=5mm, dy=5mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 9.55 V/m; Power Drift = 0.09 dB
PMR not calibrated. PMF = 2.850 is applied.
E-field emissions = 75.53 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

| | | |
|--------------------------------------|--------------------------------------|--------------------------------------|
| Grid 1 M3 73.08 V/m | Grid 2 M3 75.53 V/m | Grid 3 M3 71.21 V/m |
| Grid 4 M4 39.39 V/m | Grid 5 M3 57.24 V/m | Grid 6 M3 62.08 V/m |

| | | |
|--------------------------------------|--------------------------------------|--------------------------------------|
| Grid 7 M3 71.64 V/m | Grid 8 M2 91.79 V/m | Grid 9 M2 91.66 V/m |
|--------------------------------------|--------------------------------------|--------------------------------------|

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device_Mid_Chan/Hearing Aid

Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm
 Reference Value = 10.82 V/m; Power Drift = 0.00 dB
 PMR not calibrated. PMF = 2.850 is applied.
 E-field emissions = 72.72 V/m

Near-field category: **M3 (AWF -5 dB)**

PMF scaled E-field

| | | |
|--------------------------------------|--------------------------------------|--------------------------------------|
| Grid 1 M3 69.84 V/m | Grid 2 M3 72.72 V/m | Grid 3 M3 70.39 V/m |
| Grid 4 M4 41.04 V/m | Grid 5 M3 48.81 V/m | Grid 6 M3 57.10 V/m |
| Grid 7 M3 60.61 V/m | Grid 8 M3 83.50 V/m | Grid 9 M3 83.49 V/m |

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device_High_Chan/Hearing Aid

Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm
 Reference Value = 15.42 V/m; Power Drift = -0.04 dB
 PMR not calibrated. PMF = 2.850 is applied.
 E-field emissions = 71.79 V/m

Near-field category: **M3 (AWF -5 dB)**

PMF scaled E-field

| | | |
|--------------------------------------|--------------------------------------|--------------------------------------|
| Grid 1 M3 65.76 V/m | Grid 2 M3 71.79 V/m | Grid 3 M3 70.47 V/m |
| Grid 4 M4 | Grid 5 M3 | Grid 6 M3 |

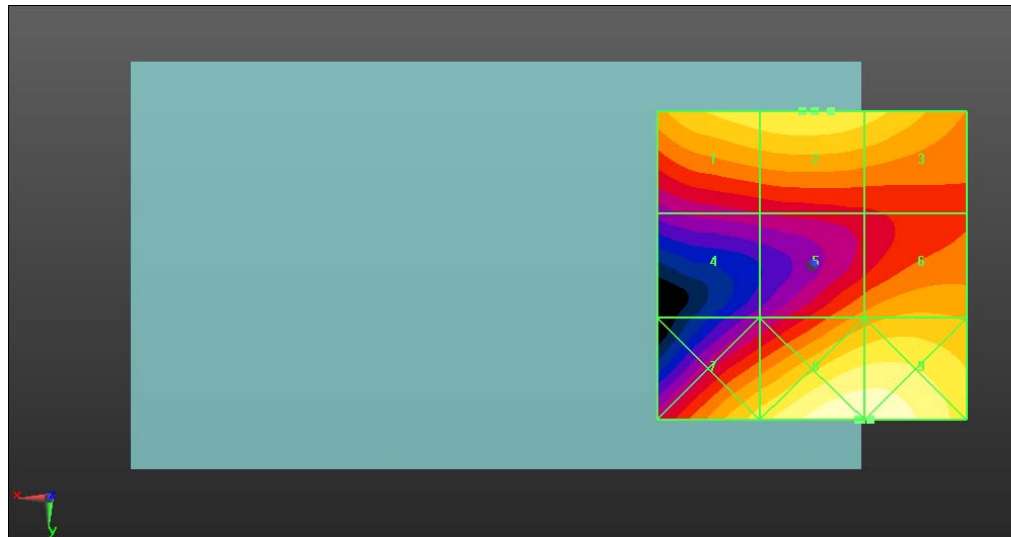
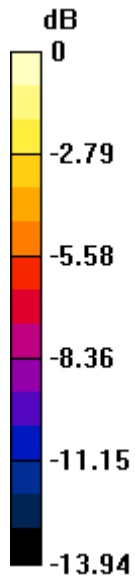
Author Data
Daoud Attayi

Dates of Test
Feb. 17, June 28, Dec. 17-18, 2012


Report No
RTS-6026-1302-03

FCC ID
L6ARFL110LW

| | | |
|------------------|------------------|------------------|
| 45.63 V/m | 48.56 V/m | 48.98 V/m |
| Grid 7 M3 | Grid 8 M3 | Grid 9 M3 |
| 52.28 V/m | 72.69 V/m | 72.77 V/m |



0 dB = 92.790V/m = 39.35 dB V/m

| | | | |
|---|--|--|--------------------------------------|
|  | Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFL111LW | | Page 72 (96) |
| | Author Data Daoud Attayi | Dates of Test Feb. 17, June 28, Dec. 17-18, 2012 | Report No RTS-6026-1302-03 |

Date/Time: 12/18/2012 9:33:03 PM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_GSM1900_Telecoil

DUT: BlackBerry Smartphone; Type: Sample ; Serial: 25CF0AD9

Communication System: GSM 1900; Frequency: 1850.2 MHz
 Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³
 Phantom section: RF Section
 Measurement Standard: DASYS (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/9/2012
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA; Serial: **Not Specified**
- DASYS2 52.8.0(692); SEMCAD X 14.6.4(4989)

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device_telecoil/Hearing Aid Compatibility Test (101x101x1):

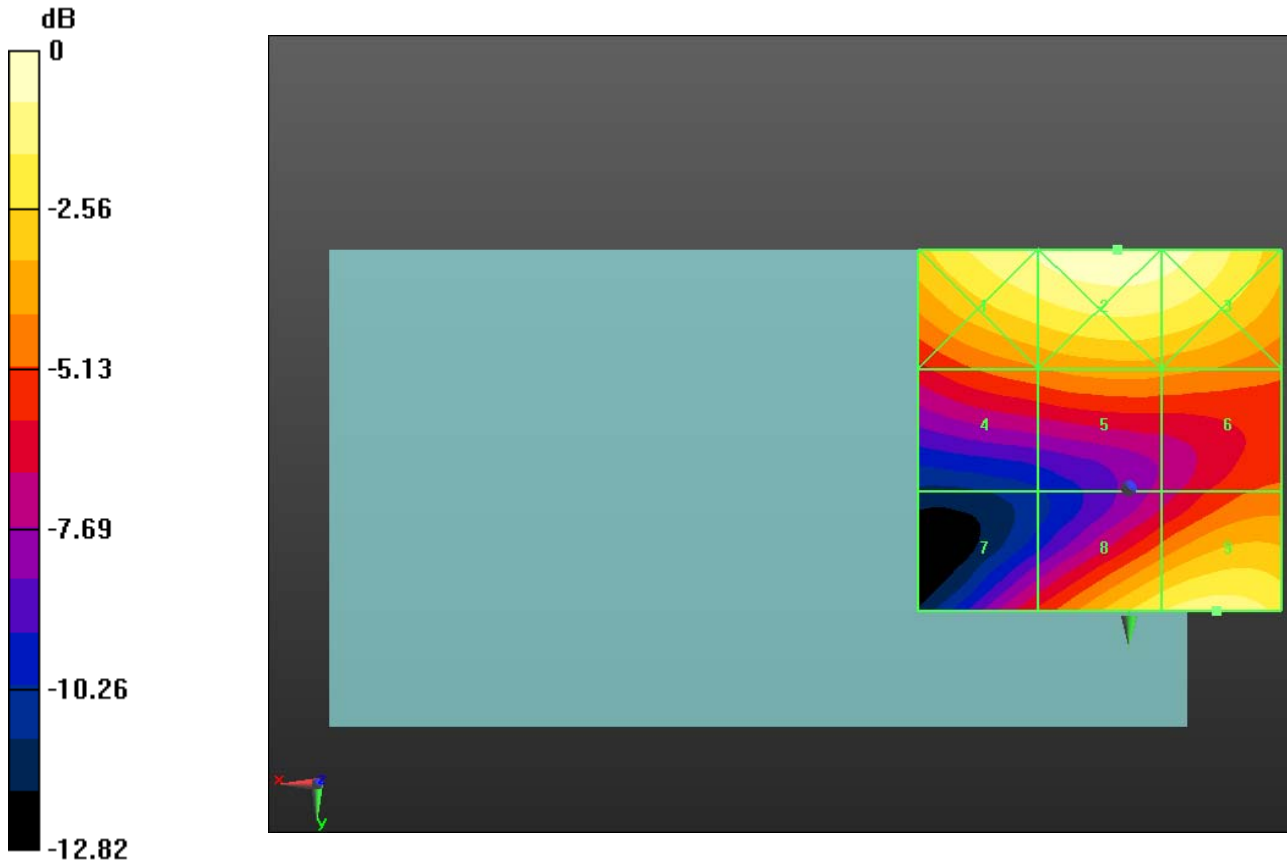
Measurement grid: dx=5mm, dy=5mm
 Device Reference Point: 0, 0, -6.3 mm
 Reference Value = 9.32 V/m; Power Drift = 0.11 dB
 PMR not calibrated. PMF = 2.850 is applied.
 E-field emissions = 75.93 V/m

Near-field category: M3 (AWF -5 dB)


PMF scaled E-field

| | | |
|--------------------------------------|--------------------------------------|--------------------------------------|
| Grid 1 M3 80.76 V/m | Grid 2 M2 86.22 V/m | Grid 3 M3 83.62 V/m |
| Grid 4 M3 52.85 V/m | Grid 5 M3 56.62 V/m | Grid 6 M3 55.54 V/m |
| Grid 7 M4 | Grid 8 M3 | Grid 9 M3 |

| | | |
|------------------|------------------|------------------|
| 45.36 V/m | 71.55 V/m | 75.93 V/m |
|------------------|------------------|------------------|



0 dB = 87.160V/m = 38.81 dB V/m

| | | | |
|---|--|--|--------------------------------------|
|  | Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFL111LW | | Page 74 (96) |
| | Author Data Daoud Attayi | Dates of Test Feb. 17, June 28, Dec. 17-18, 2012 | Report No RTS-6026-1302-03 |

Date/Time: 12/19/2012 12:14:23 AM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_GSM_1900_Telecoil_2100_Battery

DUT: BlackBerry Smartphone; Type: Sample ; Serial: 25CF0AD9

Communication System: GSM 1900; Frequency: 1850.2 MHz

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASYS (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/9/2012
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASYS2 52.8.0(692); SEMCAD X 14.6.4(4989)

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to Device_Low_Chan_telecoil_2100_Battery/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 9.84 V/m; Power Drift = 0.15 dB

PMR not calibrated. PMF = 2.850 is applied.

E-field emissions = 77.92 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

| | | |
|--------------------------------------|--------------------------------------|--------------------------------------|
| Grid 1 M2 84.17 V/m | Grid 2 M2 86.39 V/m | Grid 3 M3 82.54 V/m |
| Grid 4 M3 54.21 V/m | Grid 5 M3 55.50 V/m | Grid 6 M3 54.43 V/m |
| Grid 7 M4 | Grid 8 M3 | Grid 9 M3 |

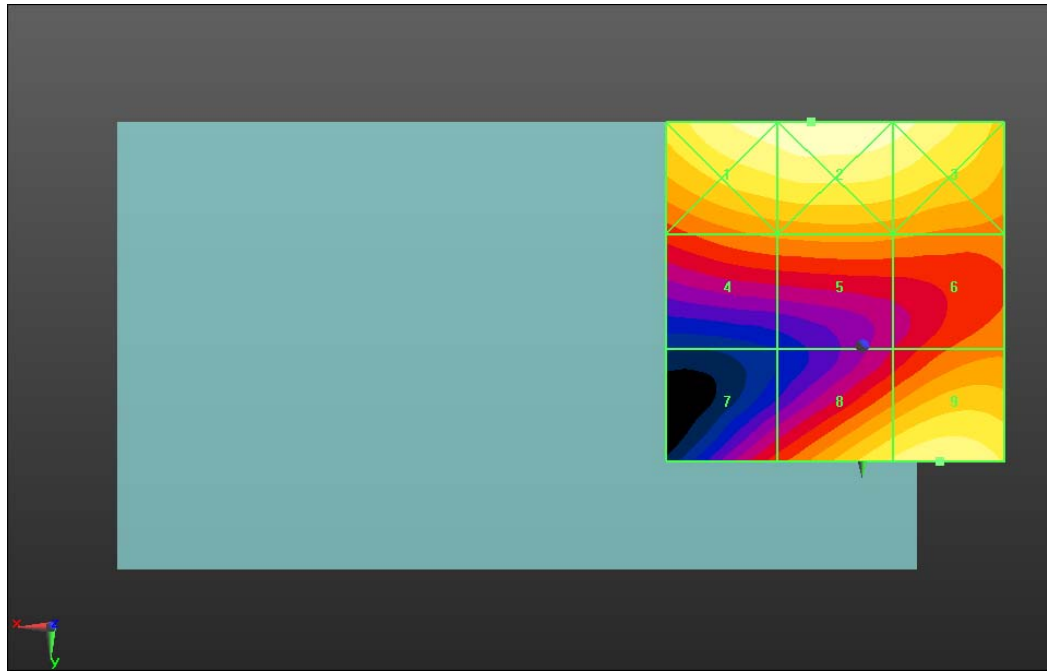
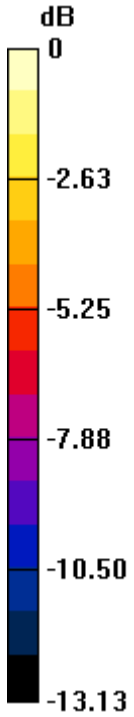
Author Data
Daoud Attayi

Dates of Test
Feb. 17, June 28, Dec. 17-18, 2012


Report No
RTS-6026-1302-03

FCC ID
L6ARFL110LW

| | | |
|------------------|------------------|------------------|
| 46.09 V/m | 72.64 V/m | 77.92 V/m |
|------------------|------------------|------------------|



0 dB = 87.330V/m = 38.82 dB V/m

| | | | |
|---|--|--|--------------------------------------|
|  | Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFL111LW | | Page 76 (96) |
| | Author Data Daoud Attayi | Dates of Test Feb. 17, June 28, Dec. 17-18, 2012 | Report No RTS-6026-1302-03 |

Date/Time: 12/18/2012 3:34:29 AM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_UMTS_Band_II

DUT: BlackBerry Smartphone; Type: Sample ; Serial: 25CF0AD9

Communication System: WCDMA FDD II; Frequency: 1852.4 MHz, Frequency: 1880 MHz, Frequency: 1907.6 MHz

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASYS (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/9/2012
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASYS2 52.8.0(692); SEMCAD X 14.6.4(4989)

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to Device_Low_Chan/Hearing Aid Compatibility Test

(101x101x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 10.50 V/m; Power Drift = 0.15 dB

PMR not calibrated. PMF = 1.000 is applied.

E-field emissions = 30.64 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

| | | |
|--------------------------------------|--------------------------------------|--------------------------------------|
| Grid 1 M4 29.21 V/m | Grid 2 M4 30.64 V/m | Grid 3 M4 28.46 V/m |
| Grid 4 M4 15.54 V/m | Grid 5 M4 20.94 V/m | Grid 6 M4 22.58 V/m |

| | | |
|--------------------------------------|--------------------------------------|--------------------------------------|
| Grid 7 M4 27.17 V/m | Grid 8 M4 34.59 V/m | Grid 9 M4 34.44 V/m |
|--------------------------------------|--------------------------------------|--------------------------------------|

Cursor:
 Total = 34.586 V/m
 E Category: M4
 Location: -6.5, 25, 8.7 mm

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device_Mid_Chan/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm
 Device Reference Point: 0, 0, -6.3 mm
 Reference Value = 13.75 V/m; Power Drift = 0.04 dB
 PMR not calibrated. PMF = 1.000 is applied.
 E-field emissions = 32.04 V/m
Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

| | | |
|--------------------------------------|--------------------------------------|--------------------------------------|
| Grid 1 M4 30.18 V/m | Grid 2 M4 32.04 V/m | Grid 3 M4 30.66 V/m |
| Grid 4 M4 17.83 V/m | Grid 5 M4 19.86 V/m | Grid 6 M4 23.27 V/m |
| Grid 7 M4 24.29 V/m | Grid 8 M4 34.52 V/m | Grid 9 M4 34.52 V/m |

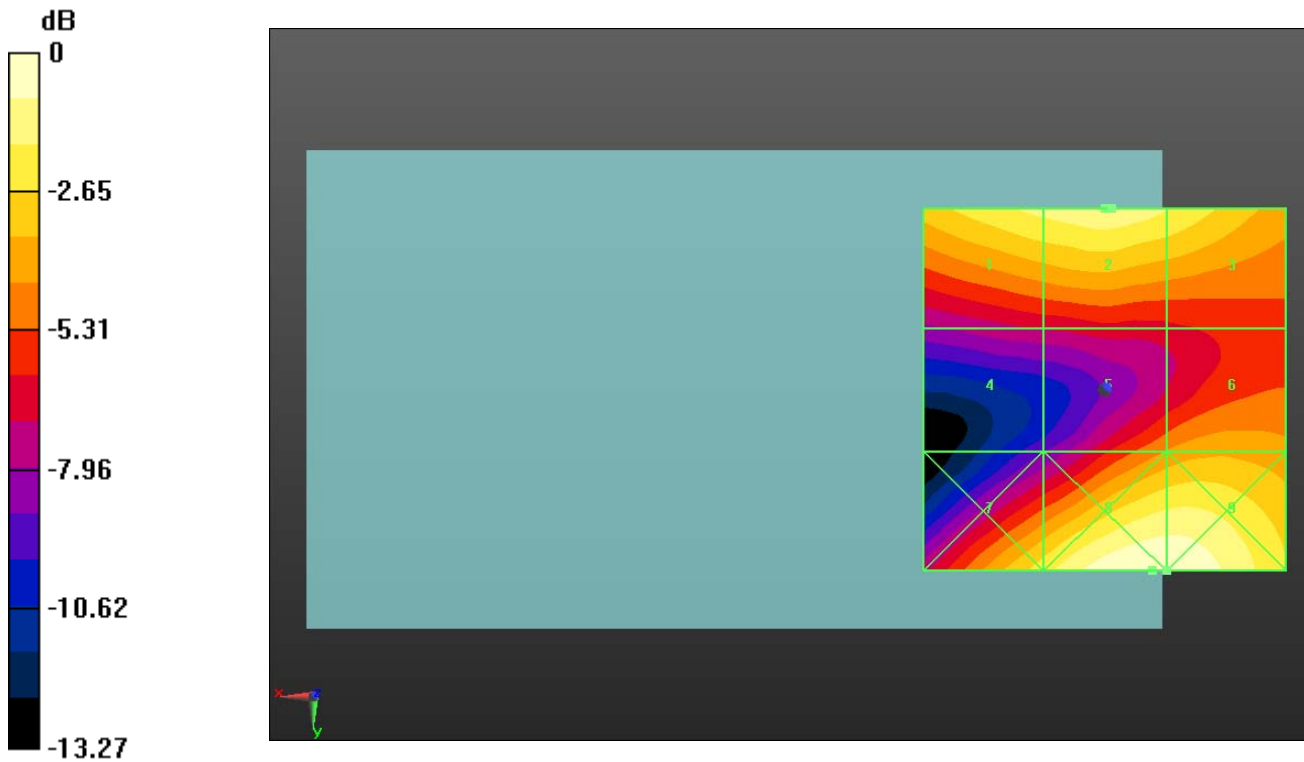
Cursor:
 Total = 34.517 V/m
 E Category: M4
 Location: -8.5, 25, 8.7 mm

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device_High_Chan/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm
 Device Reference Point: 0, 0, -6.3 mm
 Reference Value = 19.16 V/m; Power Drift = -0.03 dB
 PMR not calibrated. PMF = 1.000 is applied.
 E-field emissions = 31.28 V/m
Near-field category: M4 (AWF 0 dB)


PMF scaled E-field

| | | |
|--------------------------------------|--------------------------------------|--------------------------------------|
| Grid 1 M4 29.05 V/m | Grid 2 M4 31.28 V/m | Grid 3 M4 30.39 V/m |
| Grid 4 M4 18.78 V/m | Grid 5 M4 20.45 V/m | Grid 6 M4 20.17 V/m |
| Grid 7 M4 20.43 V/m | Grid 8 M4 29.32 V/m | Grid 9 M4 29.32 V/m |

Cursor:
 Total = 31.277 V/m
 E Category: M4
 Location: -1, -25, 8.7 mm



0 dB = 34.590V/m = 30.78 dB V/m

| | | | |
|---|--|--|--------------------------------------|
|  | Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFL111LW | | Page 79 (96) |
| | Author Data Daoud Attayi | Dates of Test Feb. 17, June 28, Dec. 17-18, 2012 | Report No RTS-6026-1302-03 |

Date/Time: 12/18/2012 11:17:23 AM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_GSM_850

DUT: BlackBerry Smartphone; Type: Sample; Serial: 25CF0AD9

Communication System: GSM 850; Frequency: 824.2 MHz, Frequency: 836.8 MHz, Frequency: 848.8 MHz

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASYS (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/9/2012
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASYS2 52.8.0(692); SEMCAD X 14.6.4(4989)

Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_low_chan/Hearing Aid Compatibility Test

(101x101x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.08 V/m; Power Drift = 0.43 dB

PMR not calibrated. PMF = 2.890 is applied.

H-field emissions = 0.49 A/m

Near-field category: M3 (AWF -5 dB)

PMF scaled H-field

| | | |
|-------------------------------------|-------------------------------------|-------------------------------------|
| Grid 1 M3 0.49 A/m | Grid 2 M4 0.34 A/m | Grid 3 M4 0.23 A/m |
| Grid 4 M4 0.41 A/m | Grid 5 M4 0.29 A/m | Grid 6 M4 0.19 A/m |



| | | | |
|------------------------------------|--|--------------------------------------|------------------------------|
| Author Data Daoud Attayi | Dates of Test Feb. 17, June 28, Dec. 17-18, 2012 | Report No RTS-6026-1302-03 | FCC ID L6ARFL110LW |
|------------------------------------|--|--------------------------------------|------------------------------|

| | | |
|-------------------------------------|-------------------------------------|-------------------------------------|
| Grid 7 M4 0.40 A/m | Grid 8 M4 0.29 A/m | Grid 9 M4 0.19 A/m |
|-------------------------------------|-------------------------------------|-------------------------------------|

Cursor:

Total = 0.487 A/m
 H Category: M3
 Location: 25, -25, 8.7 mm

Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_mid_chan/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm
 Reference Value = 0.09 V/m; Power Drift = -0.11 dB
 PMR not calibrated. PMF = 2.890 is applied.
 H-field emissions = 0.52 A/m

Near-field category: M3 (AWF -5 dB)

PMF scaled H-field

| | | |
|-------------------------------------|-------------------------------------|-------------------------------------|
| Grid 1 M3 0.52 A/m | Grid 2 M4 0.38 A/m | Grid 3 M4 0.26 A/m |
| Grid 4 M4 0.44 A/m | Grid 5 M4 0.33 A/m | Grid 6 M4 0.21 A/m |
| Grid 7 M4 0.43 A/m | Grid 8 M4 0.32 A/m | Grid 9 M4 0.19 A/m |

Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_high_chan/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

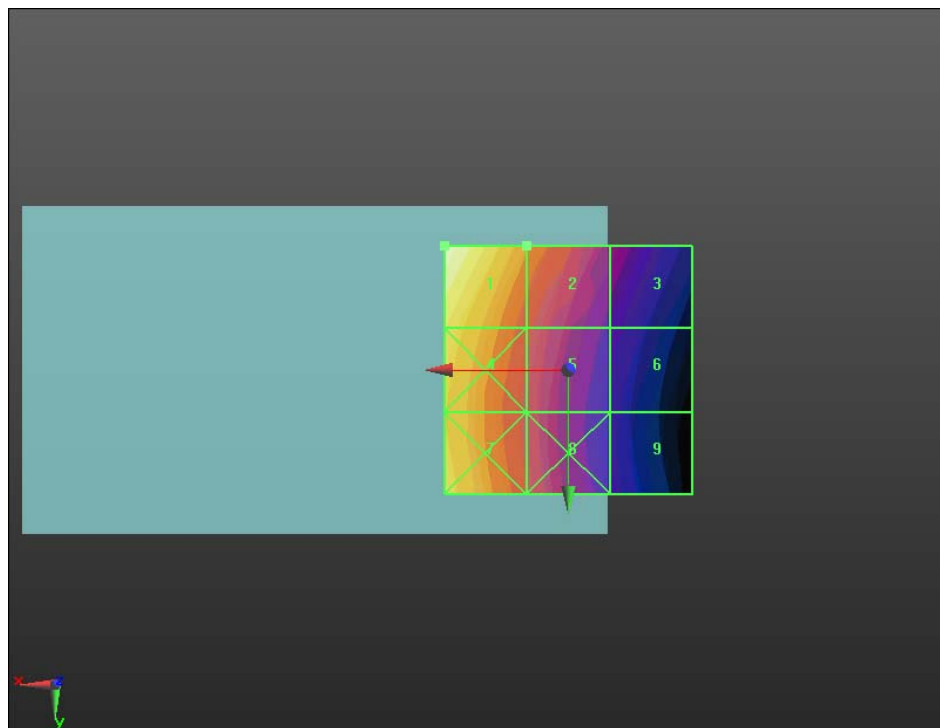
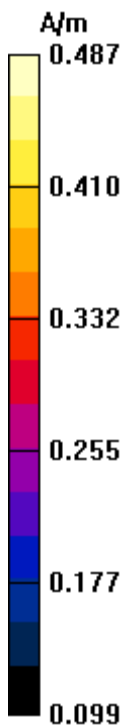
Device Reference Point: 0, 0, -6.3 mm
 Reference Value = 0.09 V/m; Power Drift = 0.06 dB
 PMR not calibrated. PMF = 2.890 is applied.
 H-field emissions = 0.51 A/m


Near-field category: M3 (AWF -5 dB)

PMF scaled H-field

| | | |
|------------------|------------------|------------------|
| Grid 1 M3 | Grid 2 M4 | Grid 3 M4 |
|------------------|------------------|------------------|

| | | |
|-------------------------------------|-------------------------------------|-------------------------------------|
| 0.51 A/m | 0.37 A/m | 0.25 A/m |
| Grid 4 M4 0.44 A/m | Grid 5 M4 0.33 A/m | Grid 6 M4 0.22 A/m |
| Grid 7 M3 0.45 A/m | Grid 8 M4 0.33 A/m | Grid 9 M4 0.22 A/m |



| | | | |
|---|--|--|--------------------------------------|
|  | Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFL111LW | | Page 82 (96) |
| | Author Data Daoud Attayi | Dates of Test Feb. 17, June 28, Dec. 17-18, 2012 | Report No RTS-6026-1302-03 |

Date/Time: 12/18/2012 8:13:49 PM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_GSM_850_Telecoil

DUT: BlackBerry Smartphone; Type: Sample; Serial: 25CF0AD9

Communication System: GSM 850; Frequency: 836.8 MHz
 Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³
 Phantom section: RF Section
 Measurement Standard: DASYS (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/9/2012
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASYS2 52.8.0(692); SEMCAD X 14.6.4(4989)

Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_Centre_Telecoil/Hearing Aid Compatibility

Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

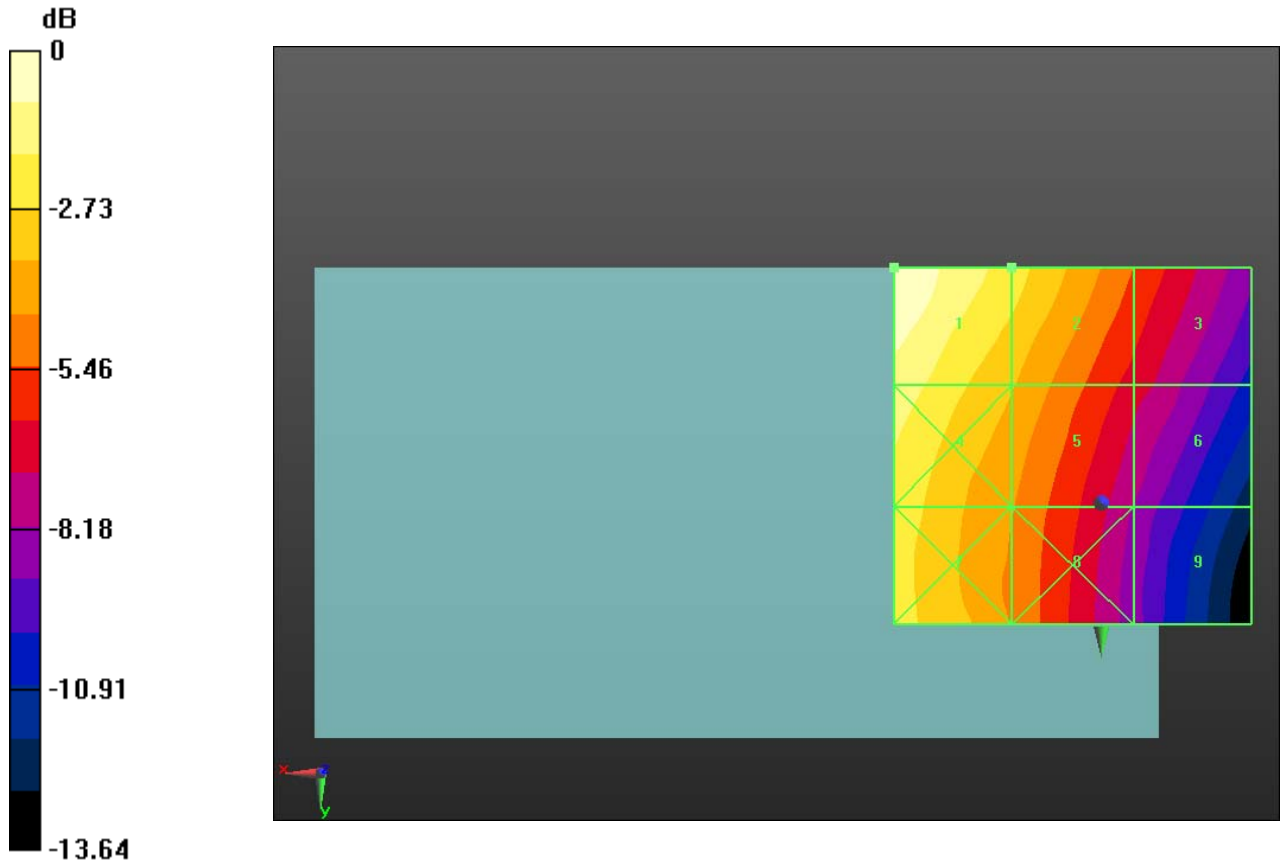
Device Reference Point: 0, 0, -6.3 mm
 Reference Value = 0.09 V/m; Power Drift = 0.06 dB
 PMR not calibrated. PMF = 2.890 is applied.
 H-field emissions = 0.56 A/m

Near-field category: M3 (AWF -5 dB)


PMF scaled H-field

| | | |
|-------------------------------------|-------------------------------------|-------------------------------------|
| Grid 1 M3 0.56 A/m | Grid 2 M4 0.43 A/m | Grid 3 M4 0.30 A/m |
| Grid 4 M3 0.48 A/m | Grid 5 M4 0.37 A/m | Grid 6 M4 0.26 A/m |
| Grid 7 M4 | Grid 8 M4 | Grid 9 M4 |

0.44 A/m 0.33 A/m 0.22 A/m



0 dB = 0.560A/m = -5.04 dB A/m

| | | | |
|---|--|--|--------------------------------------|
|  | Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFL111LW | | Page 84 (96) |
| | Author Data Daoud Attayi | Dates of Test Feb. 17, June 28, Dec. 17-18, 2012 | Report No RTS-6026-1302-03 |

Date/Time: 12/18/2012 12:06:44 PM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_UMTS_Band_V

DUT: BlackBerry Smartphone; Type: Sample; Serial: 25CF0AD9

Communication System: WCDMA FDD V; Frequency: 826.4 MHz, Frequency: 836.4 MHz, Frequency: 846.6 MHz
Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³
Phantom section: RF Section
Measurement Standard: DASYS (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/9/2012
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASYS2 52.8.0(692); SEMCAD X 14.6.4(4989)

Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_low_chan/Hearing Aid Compatibility Test

(101x101x1): Measurement grid: dx=5mm, dy=5mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.07 V/m; Power Drift = 0.11 dB
PMR not calibrated. PMF = 1.070 is applied.
H-field emissions = 0.15 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

| | | |
|-------------------------------------|-------------------------------------|-------------------------------------|
| Grid 1 M4 0.15 A/m | Grid 2 M4 0.11 A/m | Grid 3 M4 0.07 A/m |
| Grid 4 M4 0.13 A/m | Grid 5 M4 0.10 A/m | Grid 6 M4 0.06 A/m |

| | | |
|-------------------------------------|-------------------------------------|-------------------------------------|
| Grid 7 M4 0.12 A/m | Grid 8 M4 0.09 A/m | Grid 9 M4 0.05 A/m |
|-------------------------------------|-------------------------------------|-------------------------------------|

Cursor:
 Total = 0.153 A/m
 H Category: M4
 Location: 25, -25, 8.7 mm

Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_mid_chan/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm
 Device Reference Point: 0, 0, -6.3 mm
 Reference Value = 0.08 V/m; Power Drift = -0.04 dB
 PMR not calibrated. PMF = 1.070 is applied.
 H-field emissions = 0.17 A/m
Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

| | | |
|-------------------------------------|-------------------------------------|-------------------------------------|
| Grid 1 M4 0.17 A/m | Grid 2 M4 0.12 A/m | Grid 3 M4 0.08 A/m |
| Grid 4 M4 0.14 A/m | Grid 5 M4 0.11 A/m | Grid 6 M4 0.07 A/m |
| Grid 7 M4 0.14 A/m | Grid 8 M4 0.10 A/m | Grid 9 M4 0.06 A/m |

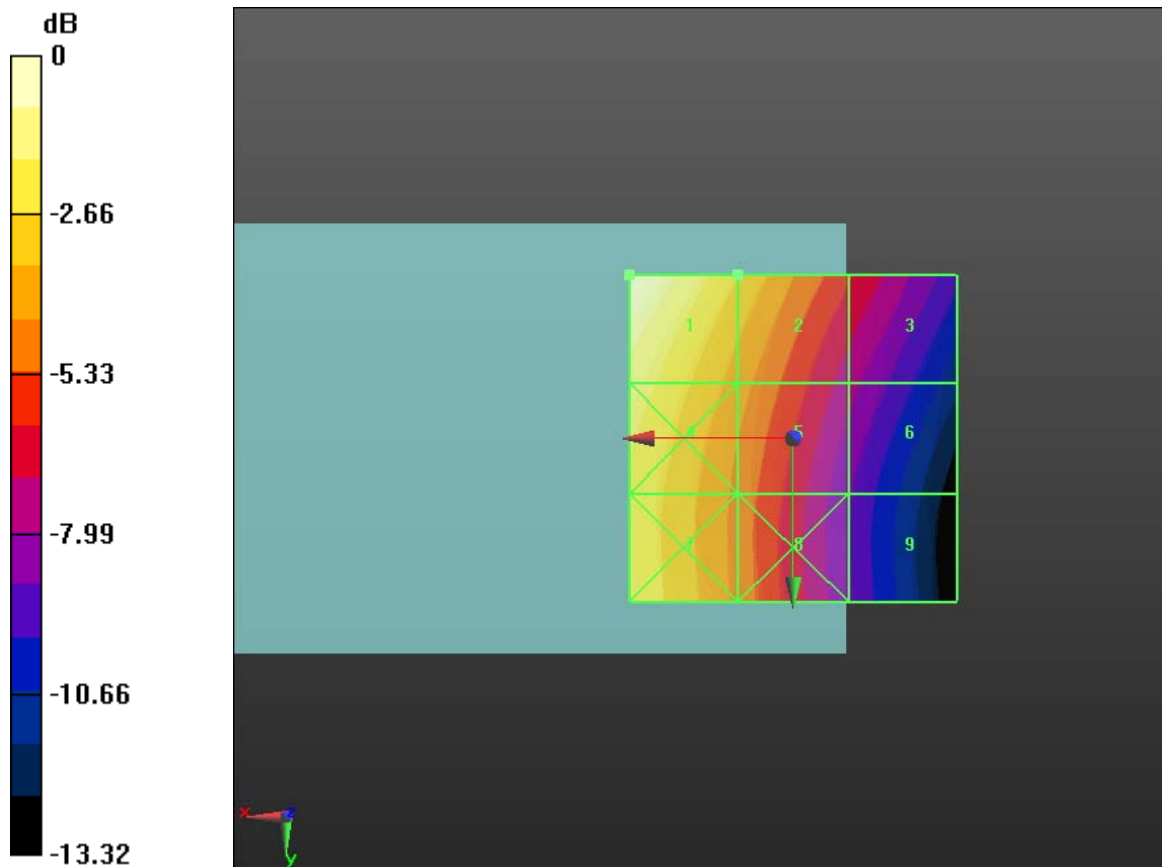
Cursor:
 Total = 0.167 A/m
 H Category: M4
 Location: 25, -25, 8.7 mm

Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_high_chan/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm
 Device Reference Point: 0, 0, -6.3 mm
 Reference Value = 0.09 V/m; Power Drift = 0.06 dB
 PMR not calibrated. PMF = 1.070 is applied.
 H-field emissions = 0.19 A/m
Near-field category: M4 (AWF 0 dB)


PMF scaled H-field

| | | |
|-------------------------------------|-------------------------------------|-------------------------------------|
| Grid 1 M4 0.19 A/m | Grid 2 M4 0.14 A/m | Grid 3 M4 0.09 A/m |
| Grid 4 M4 0.16 A/m | Grid 5 M4 0.12 A/m | Grid 6 M4 0.08 A/m |
| Grid 7 M4 0.17 A/m | Grid 8 M4 0.13 A/m | Grid 9 M4 0.08 A/m |

Cursor:
 Total = 0.186 A/m
 H Category: M4
 Location: 25, -25, 8.7 mm



0 dB = 0.150A/m = -16.48 dB A/m

| | | | |
|---|--|--|--------------------------------------|
|  | Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFL111LW | | Page 87 (96) |
| | Author Data Daoud Attayi | Dates of Test Feb. 17, June 28, Dec. 17-18, 2012 | Report No RTS-6026-1302-03 |

Date/Time: 12/18/2012 11:34:14 AM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_GSM_1900

DUT: BlackBerry Smartphone; Type: Sample; Serial: 25CF0AD9

Communication System: GSM 1900; Frequency: 1850.2 MHz, Frequency: 1880 MHz, Frequency: 1909.8 MHz
 Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³
 Phantom section: RF Section
 Measurement Standard: DASYS (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/9/2012
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASYS2 52.8.0(692); SEMCAD X 14.6.4(4989)

Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_low_chan/Hearing Aid Compatibility Test

(101x101x1): Measurement grid: dx=5mm, dy=5mm
 Device Reference Point: 0, 0, -6.3 mm
 Reference Value = 0.07 V/m; Power Drift = 0.19 dB
 PMR not calibrated. PMF = 2.860 is applied.
 H-field emissions = 0.22 A/m

Near-field category: M3 (AWF -5 dB)

PMF scaled H-field

| | | |
|-------------------------------------|-------------------------------------|-------------------------------------|
| Grid 1 M3 0.21 A/m | Grid 2 M3 0.21 A/m | Grid 3 M3 0.22 A/m |
| Grid 4 M3 0.16 A/m | Grid 5 M3 0.22 A/m | Grid 6 M3 0.22 A/m |



| | | | |
|------------------------------------|--|--------------------------------------|------------------------------|
| Author Data Daoud Attayi | Dates of Test Feb. 17, June 28, Dec. 17-18, 2012 | Report No RTS-6026-1302-03 | FCC ID L6ARFL110LW |
|------------------------------------|--|--------------------------------------|------------------------------|

| | | |
|-------------------------------------|-------------------------------------|-------------------------------------|
| Grid 7 M3 0.20 A/m | Grid 8 M3 0.20 A/m | Grid 9 M3 0.20 A/m |
|-------------------------------------|-------------------------------------|-------------------------------------|

Cursor:

Total = 0.218 A/m
 H Category: M3
 Location: -11, -5.5, 8.7 mm

Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_mid_chan/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm
 Reference Value = 0.07 V/m; Power Drift = -0.14 dB
 PMR not calibrated. PMF = 2.860 is applied.
 H-field emissions = 0.21 A/m

Near-field category: M3 (AWF -5 dB)

PMF scaled H-field

| | | |
|-------------------------------------|-------------------------------------|-------------------------------------|
| Grid 1 M3 0.20 A/m | Grid 2 M3 0.20 A/m | Grid 3 M3 0.21 A/m |
| Grid 4 M3 0.16 A/m | Grid 5 M3 0.21 A/m | Grid 6 M3 0.21 A/m |
| Grid 7 M3 0.20 A/m | Grid 8 M3 0.20 A/m | Grid 9 M3 0.20 A/m |

Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_high_chan/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

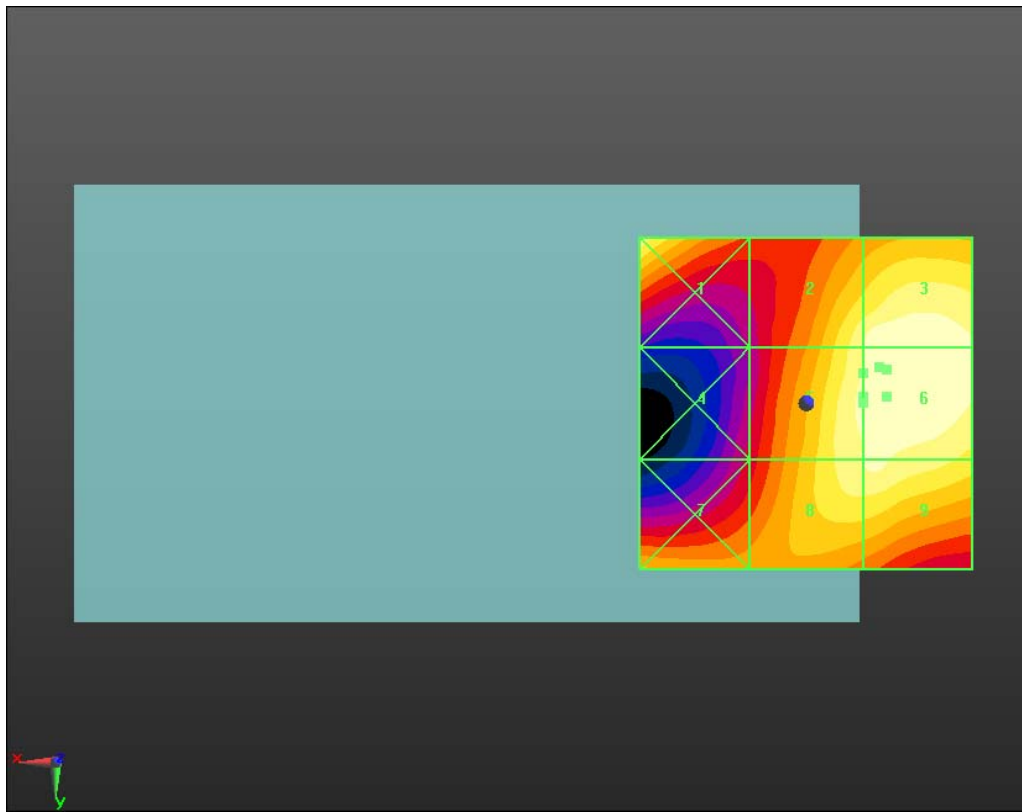
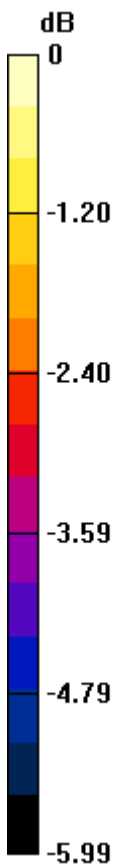
Device Reference Point: 0, 0, -6.3 mm
 Reference Value = 0.07 V/m; Power Drift = 0.07 dB
 PMR not calibrated. PMF = 2.860 is applied.
 H-field emissions = 0.21 A/m

Near-field category: M3 (AWF -5 dB)


PMF scaled H-field

| | | |
|------------------|------------------|------------------|
| Grid 1 M3 | Grid 2 M3 | Grid 3 M3 |
|------------------|------------------|------------------|

| | | |
|-------------------------------------|-------------------------------------|-------------------------------------|
| 0.20 A/m | 0.20 A/m | 0.21 A/m |
| Grid 4 M3 0.14 A/m | Grid 5 M3 0.20 A/m | Grid 6 M3 0.21 A/m |
| Grid 7 M3 0.17 A/m | Grid 8 M3 0.20 A/m | Grid 9 M3 0.20 A/m |



0 dB = 0.220A/m = -13.15 dB A/m

| | | | |
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|  | Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFL111LW | | Page 90 (96) |
| | Author Data Daoud Attayi | Dates of Test Feb. 17, June 28, Dec. 17-18, 2012 | Report No RTS-6026-1302-03 |

Date/Time: 12/18/2012 8:33:13 PM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_GSM_1900_Telecoil

DUT: BlackBerry Smartphone; Type: Sample; Serial: 25CF0AD9

Communication System: GSM 1900; Frequency: 1850.2 MHz

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

Measurement Standard: DASYS (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/9/2012
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASYS2 52.8.0(692); SEMCAD X 14.6.4(4989)

Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_Centre_Telecoil/Hearing Aid Compatibility

Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.08 V/m; Power Drift = -0.08 dB

PMR not calibrated. PMF = 2.860 is applied.

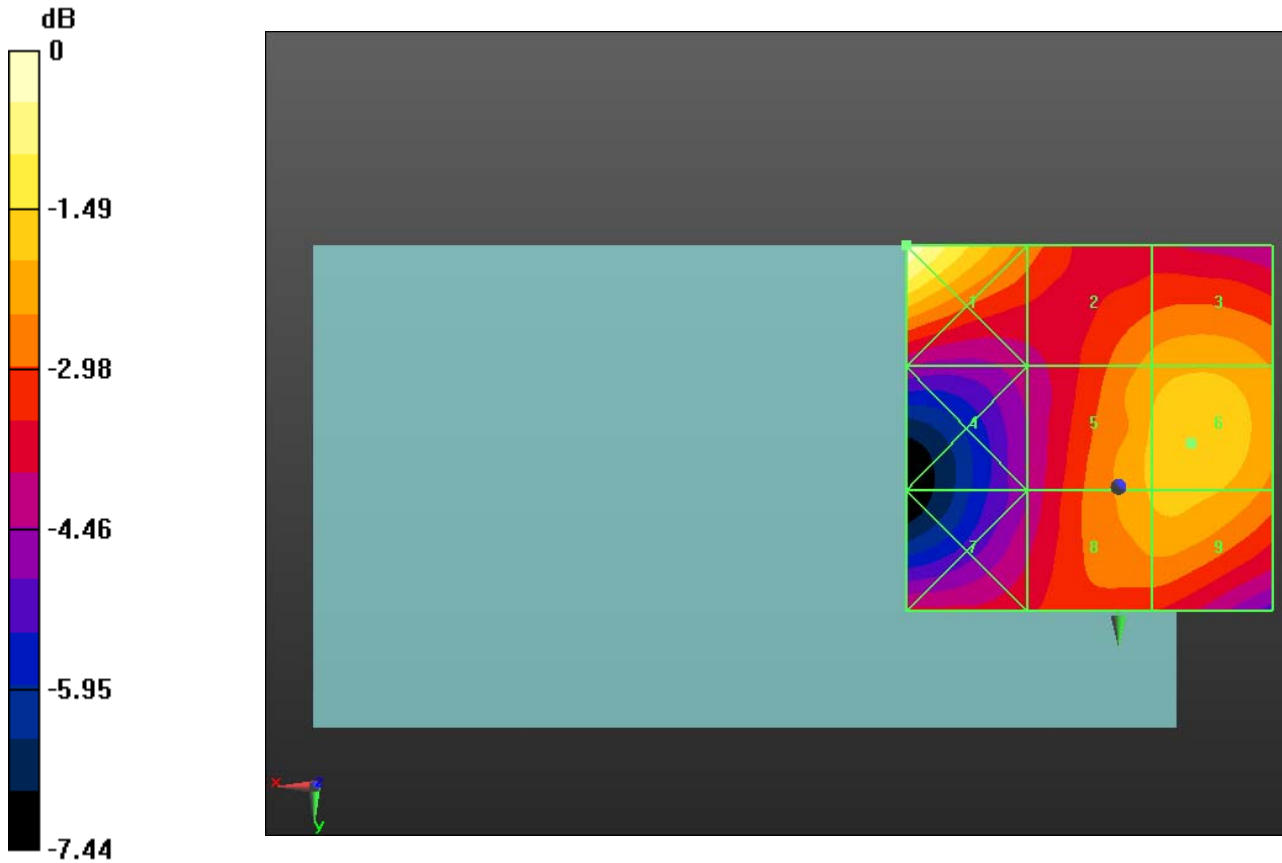
H-field emissions = 0.22 A/m

Near-field category: M3 (AWF -5 dB)


PMF scaled H-field

| | | |
|-------------------------------------|-------------------------------------|-------------------------------------|
| Grid 1 M2 0.27 A/m | Grid 2 M3 0.21 A/m | Grid 3 M3 0.21 A/m |
| Grid 4 M3 0.17 A/m | Grid 5 M3 0.22 A/m | Grid 6 M3 0.22 A/m |
| Grid 7 M3 | Grid 8 M3 | Grid 9 M3 |

0.18 A/m 0.22 A/m 0.22 A/m



0 dB = 0.270A/m = -11.37 dB A/m

| | | | |
|---|--|--|--------------------------------------|
|  | Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFL111LW | | Page 92 (96) |
| | Author Data Daoud Attayi | Dates of Test Feb. 17, June 28, Dec. 17-18, 2012 | Report No RTS-6026-1302-03 |

Date/Time: 12/18/2012 11:45:55 PM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_GSM_1900_Telecoil_2100_Battery

DUT: BlackBerry Smartphone; Type: Sample; Serial: 25CF0AD9

Communication System: GSM 1900; Frequency: 1850.2 MHz
Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³
Phantom section: RF Section
Measurement Standard: DASYS (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/9/2012
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASYS2 52.8.0(692); SEMCAD X 14.6.4(4989)

Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_Centre_Telecoil_2100_Battery/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

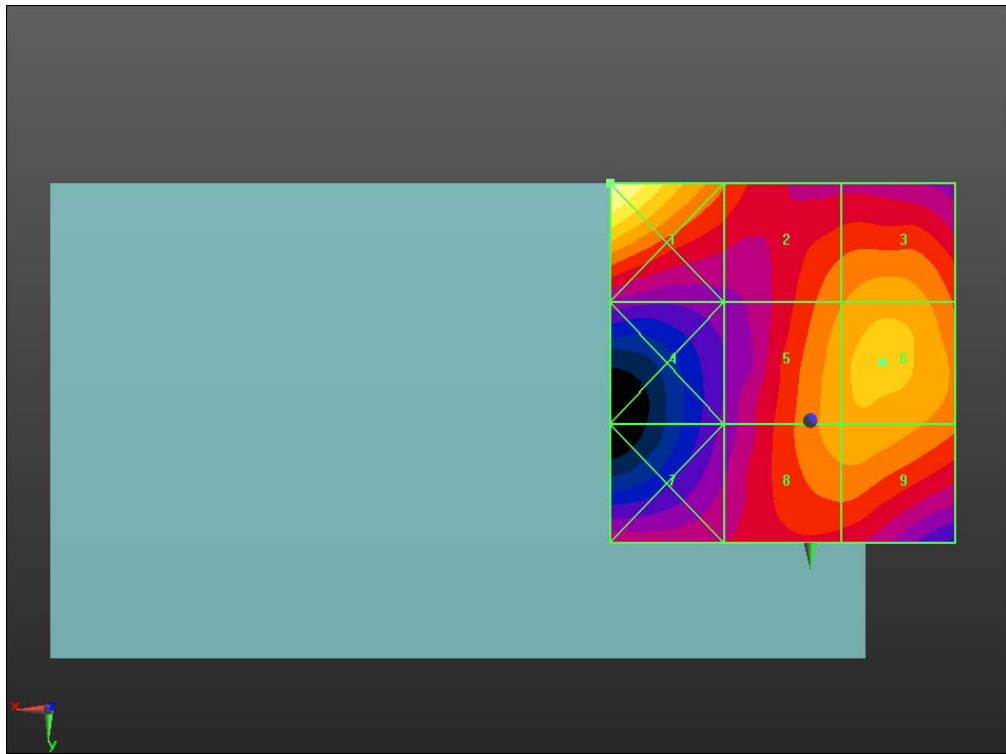
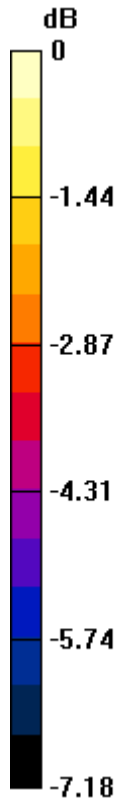
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.08 V/m; Power Drift = -0.06 dB
PMR not calibrated. PMF = 2.860 is applied.
H-field emissions = 0.22 A/m

Near-field category: M3 (AWF -5 dB)


PMF scaled H-field

| | | |
|-------------------------------------|-------------------------------------|-------------------------------------|
| Grid 1 M2 0.27 A/m | Grid 2 M3 0.20 A/m | Grid 3 M3 0.21 A/m |
| Grid 4 M3 0.16 A/m | Grid 5 M3 0.21 A/m | Grid 6 M3 0.22 A/m |
| Grid 7 M3 | Grid 8 M3 | Grid 9 M3 |

0.17 A/m **0.21 A/m** **0.22 A/m**



0 dB = 0.270A/m = -11.37 dB A/m

| | | | |
|---|--|--|--------------------------------------|
|  | Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFL111LW | | Page 94 (96) |
| | Author Data Daoud Attayi | Dates of Test Feb. 17, June 28, Dec. 17-18, 2012 | Report No RTS-6026-1302-03 |

Date/Time: 12/18/2012 11:49:35 AM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_UMTS_Band_II

DUT: BlackBerry Smartphone; Type: Sample; Serial: 25CF0AD9

Communication System: WCDMA FDD II; Frequency: 1852.4 MHz, Frequency: 1880 MHz, Frequency: 1907.6 MHz
 Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³
 Phantom section: RF Section
 Measurement Standard: DASYS (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/9/2012
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASYS2 52.8.0(692); SEMCAD X 14.6.4(4989)

Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_low_chan/Hearing Aid Compatibility Test

(101x101x1): Measurement grid: dx=5mm, dy=5mm
 Device Reference Point: 0, 0, -6.3 mm
 Reference Value = 0.08 V/m; Power Drift = 0.06 dB
 PMR not calibrated. PMF = 1.000 is applied.
 H-field emissions = 0.09 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

| | | |
|-------------------------------------|-------------------------------------|-------------------------------------|
| Grid 1 M4 0.08 A/m | Grid 2 M4 0.08 A/m | Grid 3 M4 0.09 A/m |
| Grid 4 M4 0.07 A/m | Grid 5 M4 0.09 A/m | Grid 6 M4 0.09 A/m |

| | | |
|-------------------------------------|-------------------------------------|-------------------------------------|
| Grid 7 M4 0.08 A/m | Grid 8 M4 0.08 A/m | Grid 9 M4 0.08 A/m |
|-------------------------------------|-------------------------------------|-------------------------------------|

Cursor:
 Total = 0.087 A/m
 H Category: M4
 Location: -12, -5, 8.7 mm

Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_mid_chan/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm
 Device Reference Point: 0, 0, -6.3 mm
 Reference Value = 0.08 V/m; Power Drift = 0.06 dB
 PMR not calibrated. PMF = 1.000 is applied.
 H-field emissions = 0.09 A/m
Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

| | | |
|-------------------------------------|-------------------------------------|-------------------------------------|
| Grid 1 M4 0.08 A/m | Grid 2 M4 0.09 A/m | Grid 3 M4 0.09 A/m |
| Grid 4 M4 0.07 A/m | Grid 5 M4 0.09 A/m | Grid 6 M4 0.09 A/m |
| Grid 7 M4 0.09 A/m | Grid 8 M4 0.08 A/m | Grid 9 M4 0.08 A/m |

Cursor:
 Total = 0.090 A/m
 H Category: M4
 Location: -12, -4, 8.7 mm

Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_high_chan/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm
 Device Reference Point: 0, 0, -6.3 mm
 Reference Value = 0.08 V/m; Power Drift = 0.23 dB
 PMR not calibrated. PMF = 1.000 is applied.
 H-field emissions = 0.09 A/m
Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Author Data
Daoud Attayi

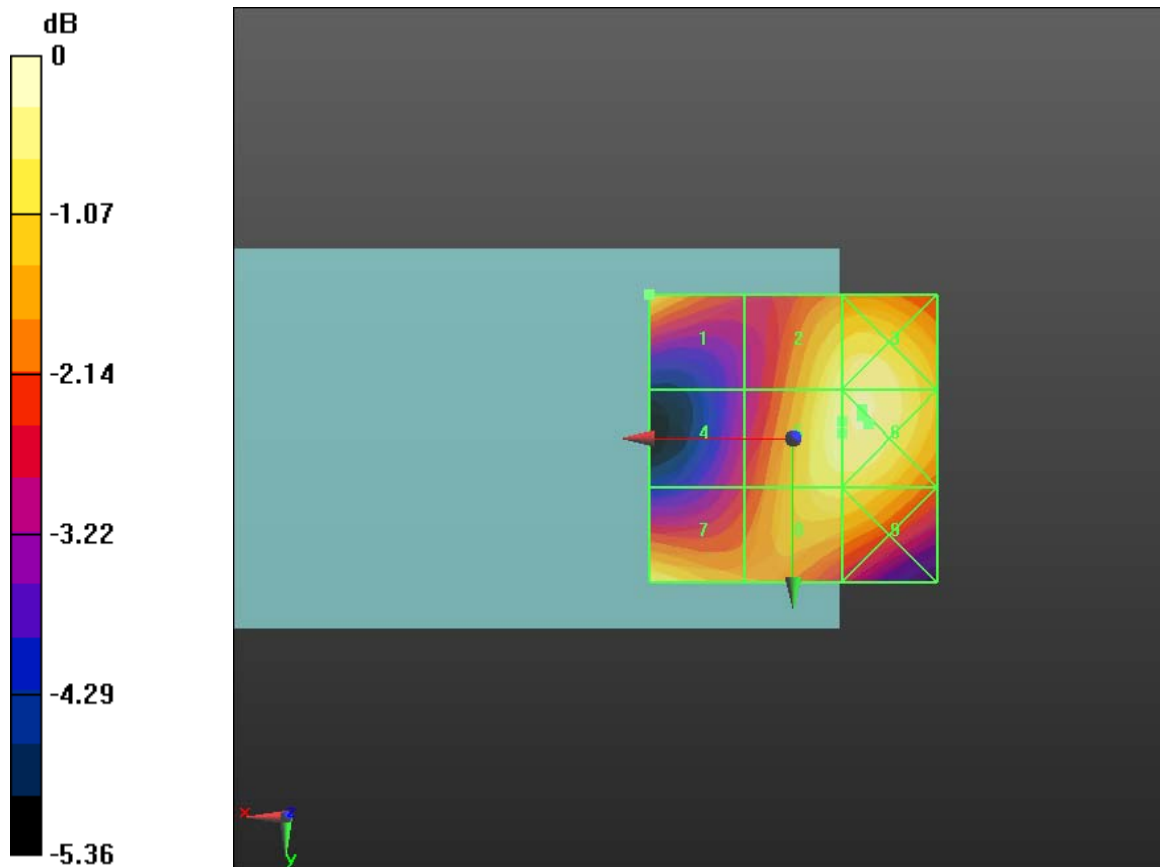
Dates of Test
Feb. 17, June 28, Dec. 17-18, 2012

Report No
RTS-6026-1302-03

FCC ID
L6ARFL110LW

| | | |
|-------------------------------------|-------------------------------------|-------------------------------------|
| Grid 1 M4 0.09 A/m | Grid 2 M4 0.08 A/m | Grid 3 M4 0.08 A/m |
| Grid 4 M4 0.06 A/m | Grid 5 M4 0.08 A/m | Grid 6 M4 0.09 A/m |
| Grid 7 M4 0.07 A/m | Grid 8 M4 0.08 A/m | Grid 9 M4 0.08 A/m |

Cursor:
 Total = 0.086 A/m
 H Category: M4
 Location: -13, -2.5, 8.7 mm



0 dB = 0.090A/m = -20.92 dB A/m